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## Description

The F2480 is a 400 to 3000 MHz RF Analog Variable Gain Amplifier (AVGA) that can be used in receivers, transmitters and other applications. Either the amplifier or voltage variable attenuator (VVA) can be configured as the first stage in the cascade.

The F2480 RF AVGA provides 12dB typical maximum cascade gain (no attenuation) with 4.3dB noise figure (amplifier as first stage) and 36dB gain adjustment designed to operate with a single +5V supply. Nominally, the amplifier offers +41.5dBm output IP3 using 106mA of  $I_{CC}$ .

This device is packaged in a 5 x 5 mm, 32-pin TQFN with 50Ω single-ended RF input and RF output impedances for ease of integration into the signal-path lineup.

## Competitive Advantage

The F2480 RF AVGA provides very high-performance by combining a silicon VVA & a *Zero-Distortion™* RF amplifier in a single, compact TQFN package. Because of the superb VVA IP3 performance over its full attenuation range, the VVA can be placed after the amplifier while yielding the desired cascaded OIP3 performance. Utilizing IDT's technology, the resultant RF AVGA provides +41.5dBm OIP3 performance at 900MHz. The device is internally matched so there is no need to optimize external matching elements.

## Typical Applications

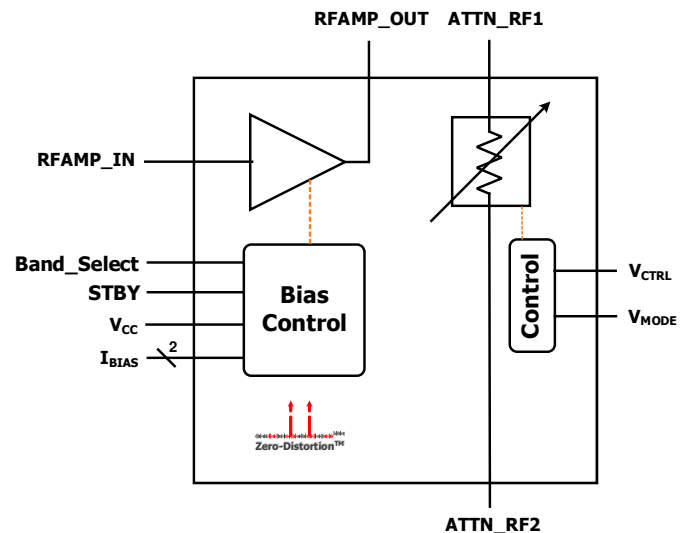
- Multi-mode, Multi-carrier Receivers
- PCS1900 Base Stations
- DCS1800 Base Stations
- WiMAX and LTE Base Stations
- UMTS/WCDMA 3G Base Stations
- PHS/PAS Base Stations
- Point to Point Infrastructure
- Public Safety Infrastructure
- Broadband Repeaters
- GPS Receivers
- Distributed Antenna Systems
- Cable Infrastructure
- Digital Radio

## Features

- 400 to 3000 MHz (Amplifier Range)
- 50 to 6000 MHz (Attenuator Range)
- 12dB typical cascaded max gain
- 36dB continuous gain range
- Excellent linearity +41.5dBm OIP3
- Noise Figure 4.3dB
- $I_{CC} = 106\text{mA}$
- 1.2mA Amplifier Standby Current
- Bi-directional attenuator RF ports
- Positive amplifier gain slope vs. frequency to counteract system PCB loss.
- $V_{MODE}$  pin allows either positive or negative attenuation control response
- Linear-in-dB attenuation characteristic
- 4 RF Port pinout supporting multiple lineup configurations
- 50Ω input and output impedances
- Broadband, Internally Matched
- 5 x 5 mm, 32-pin TQFN package

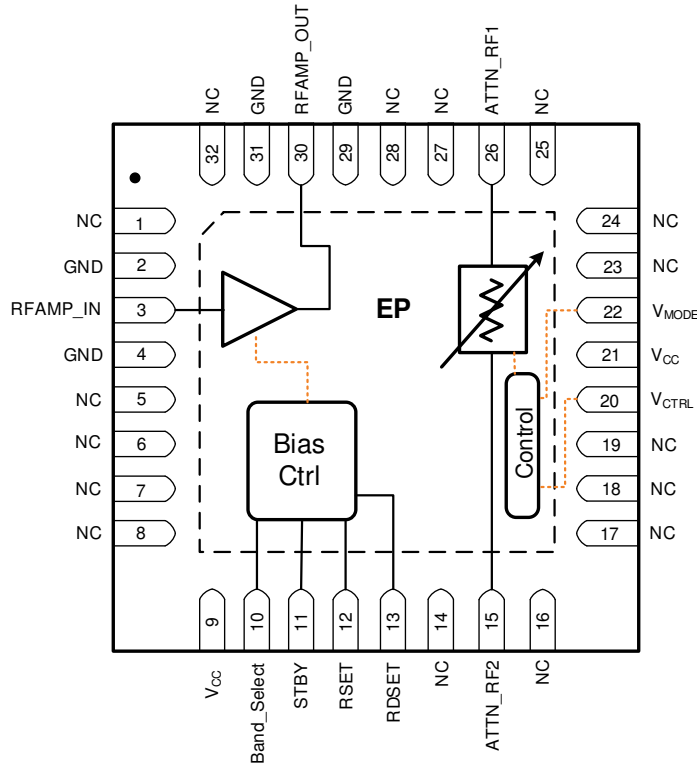
## Block Diagram

Figure 1. Block Diagram



## Pin Assignments

Figure 2. Pin Assignments for 5 x 5 x 0.75 mm - TQFN Package - Top View



## Pin Descriptions

**Table 1. Pin Descriptions**

Number	Name	Description
1, 5, 6, 7, 8, 14, 16, 17, 18, 19, 23, 24, 25, 27, 28, 32	NC	No internal connection. These pins can be left unconnected, have voltage applied, or connected to ground (recommended).
2, 4, 29, 31	GND	Ground these pins. These pins are internally connected to the exposed paddle.
3	RFAMP_IN	Amplifier input internally matched to 50Ω. Must use external DC block.
9	V <sub>CC</sub>	+5V Power Supply. Tie to V <sub>CC</sub> and connect bypass capacitors as close to the pin as possible. See Typical Application Circuit for details.
10	Band_Select	Leave pin open circuited for low-band select and connect 0Ω resistor to GND for mid-band, high-band and wide-band applications. A pull-up resistor of approximately 1.5MΩ connects between this pin and V <sub>CC</sub> .
11	STBY	Logic Low or Open on this pin enables the device. Logic High puts the device into Standby mode. A pull-down resistor of approximately 1MΩ connects between this pin and GND.
12	RSET	Connect external resistor to GND to optimize amplifier bias. Used in conjunction with pin 13.
13	RDSET	Connect external resistor to GND to optimize amplifier bias. Used in conjunction with pin 12.
15	ATTN_RF2	Attenuator RF Port 2. Matched to 50Ω. Use an external DC blocking capacitor as close to the device as possible.
20	V <sub>CTRL</sub>	Attenuator control voltage. Apply a voltage in the range as specified in the General Specifications Table. See application section for details about V <sub>CTRL</sub> . This pin has an internal pull down resistor.
21	V <sub>CC</sub>	+5V Power Supply. Tie to V <sub>CC</sub> and connect bypass capacitors as close to the pin as possible. See Typical Application Circuit for details.
22	V <sub>MODE</sub>	Attenuator slope control. Set to logic LOW to enable negative attenuation slope (Attenuation low to high as voltage is increased). Set to logic HIGH to enable positive attenuation slope (Attenuation high to low as voltage is increased).
26	ATTN_RF1	Attenuator RF Port 1. Matched to 50Ω. Use an external DC blocking capacitor as close to the device as possible.
30	RFAMP_OUT	Amplifier output internally matched to 50Ω. Must use external DC block as close to the pin as possible.
	— EP	Exposed Pad. Internally connected to GND. Solder this exposed pad to a PCB pad that uses multiple ground vias to provide heat transfer out of the device into the PCB ground planes. These multiple ground vias are also required to achieve the noted RF performance.

## Absolute Maximum Ratings

The absolute maximum ratings are stress ratings only. Stresses greater than those listed below can cause permanent damage to the device. Functional operation of the F2480 at absolute maximum ratings is not implied. Exposure to absolute maximum rating conditions may affect device reliability.

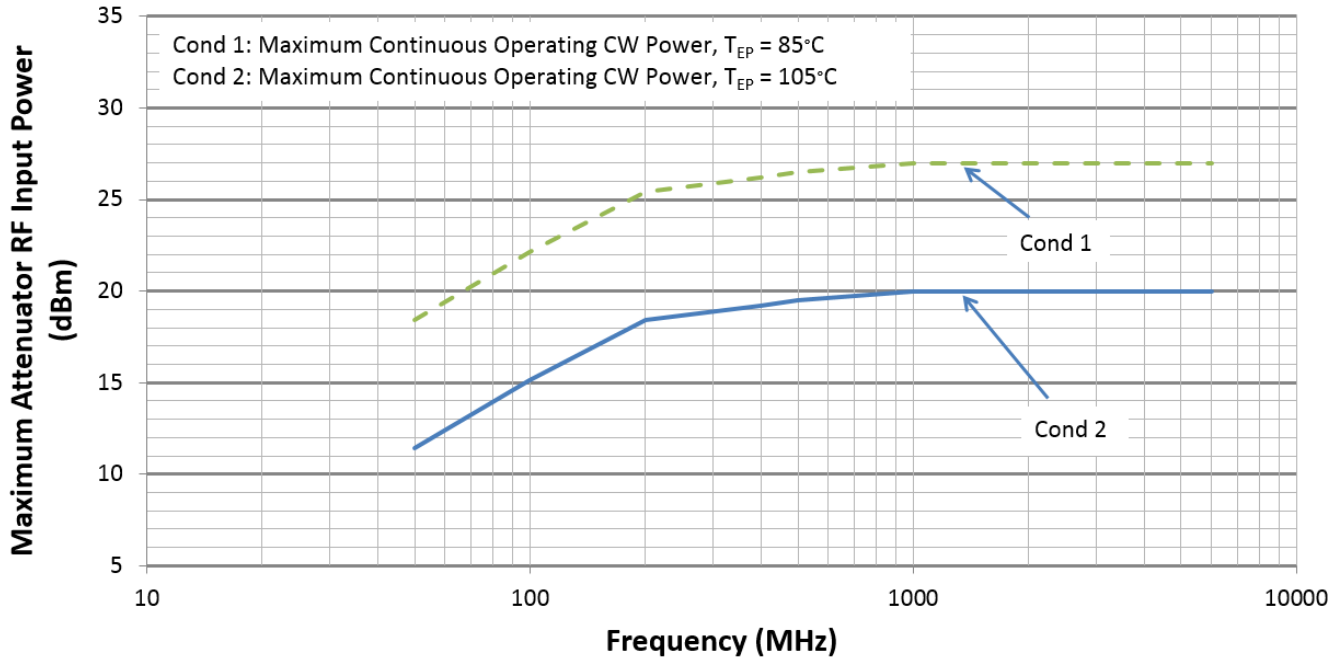
**Table 2. Absolute Maximum Ratings**

Parameter	Symbol	Minimum	Maximum	Units
V <sub>CC</sub> to GND	V <sub>CC</sub>	-0.3	5.5	V
STBY, Band_Select	V <sub>LOGIC</sub>	-0.3	V <sub>CC</sub> + 0.25	V
RSET	I <sub>RSET</sub>		+1.5	mA
RDSET	I <sub>RDSET</sub>		+0.8	mA
RFAMP_IN externally applied DC voltage	V <sub>RFAMPin</sub>	+1.4	+3.6	V
RFAMP_OUT externally applied DC voltage	V <sub>RFAMPout</sub>	V <sub>CC</sub> - 0.15	V <sub>CC</sub> + 0.15	V
V <sub>MODE</sub> to GND	V <sub>MODE</sub>	-0.3	Lower of (V <sub>CC</sub> , 3.9)	V
V <sub>CTRL</sub> to GND (V <sub>CC</sub> = 0 to 5.25 V)	V <sub>CTRL</sub>	-0.3	Lower of (V <sub>CC</sub> , 4.0)	V
ATTEN_RF1, ATTEN_RF2	V <sub>ATTENRF</sub>	-0.3	+0.3	V
RFAMP_IN RF Input Power applied for 24 hours maximum (V <sub>CC</sub> applied, RF = 2GHz, T <sub>A</sub> =+25°C)	P <sub>MAXAMP</sub>		+22	dBm
ATTN_RF1 or ATTN_RF2 RF Input Power (@ 2GHz and +85°C)	P <sub>MAXATTEN</sub>		+30	dBm
Continuous Power Dissipation	P <sub>diss</sub>		1.5	W
Junction Temperature	T <sub>j</sub>		+150	°C
Storage Temperature Range	T <sub>st</sub>	-65	+150	°C
Lead Temperature (soldering, 10s)			+260	°C
Electrostatic Discharge – HBM (JEDEC/ESDA JS-001-2014)			Class 1C	
Electrostatic Discharge – CDM (JEDEC 22-C101F)			Class C3	

## Recommended Operating Conditions

**Table 3. Recommended Operating Conditions**

Parameter	Symbol	Condition	Minimum	Typical	Maximum	Units
Power Supply Voltage	$V_{CC}$	All $V_{CC}$ Pins	4.75	5.00	5.25	V
Operating Temperature Range	$T_{EP}$	Exposed Paddle Temperature	-40		+105	°C
RF Frequency Range	$f_{RF}$	Amplifier	400		3000	MHz
		Attenuator	50		6000	
Amplifier RF Maximum Input Operating Power	$P_{max1, CW}$	$T_{EP} = -40$ to $105$ °C			8	dBm
Attenuator RF Maximum Input Operating Power	$P_{max2, CW}$	ATTEN_RF1 or ATTEN_RF2			See Figure 3	dBm
RFAMP_IN Port Impedance	$Z_{RFAMPIN}$			50		$\Omega$
RFAMP_OUT Port Impedance	$Z_{RFAMPOUT}$			50		$\Omega$
ATTN_RF1 Port Impedance	$Z_{ATTNRF1}$			50		$\Omega$
ATTN_RF2 Port Impedance	$Z_{ATTNRF2}$			50		$\Omega$

**Figure 3. Attenuator Maximum RF Input Power vs. Frequency**


## Electrical Characteristics

**Table 4. General Electrical Characteristics**

Parameter	Symbol	Condition	Minimum	Typical	Maximum	Units
Logic Input High Threshold	$V_{IH\_AMP}$	STBY, Band_Select	<b>1.1</b> <sup>[a]</sup>		$V_{CC}$ <sup>[b]</sup>	V
Logic Input Low Threshold	$V_{IL\_AMP}$	STBY, Band_Select	<b>-0.3</b>		<b>0.63</b>	V
$V_{MODE}$ Logic	$V_{IH\_Mode}$	$V_{CC} > 3.9V$	1.17		3.6	V
		$3.15V \leq V_{CC} \leq 3.9V$	1.17		$V_{CC} - 0.3$	
	$V_{IL\_Mode}$		0		0.63	
$V_{CTRL}$ Voltage	$V_{CTRL}$	$3.9V < V_{CC} \leq 5.25V$	0		3.6	V
		$3.15V \leq V_{CC} \leq 3.9V$	0		$V_{CC} - 0.3$	
Logic Current	$I_{STBY}$		<b>-10</b>		<b>12</b>	$\mu A$
	$I_{Band\_Select}$		<b>-10</b>		<b>10</b>	
	$I_{MODE}$		<b>-1</b>		<b>35</b>	
Control Current	$I_{CTRL}$	Pin 20	<b>-1</b>		<b>12</b>	$\mu A$
Supply Current	$I_{CC}$	Pin 21	<b>0.90</b>	1.17	<b>2.20</b>	mA
		Pin 9 – Low Band Bias		106		
		Pin 9 – Mid Band Bias		121	<b>170</b>	
		Pin 9 – High Band Bias		121		
		Pin 9 – Wide Band Bias		121		
		Pin 9 – Standby		0.8	<b>1.7</b>	
Startup Time from STBY		50% of STBY going low to Gain within $\pm 1dB$		250		ns

a. Items in min/max columns in **bold italics** are guaranteed by test.

b. Items in min/max columns that are not bold/italics are guaranteed by design characterization.

**Table 5. Stand Alone Amplifier Electrical Characteristics**

Typical Application Circuit. See Table 8 band settings as noted (LB, MB, HB, WB),  $V_{CC} = +5.0V$ ,  $T_{EP} = +25^{\circ}C$ ,  $f_{RF} = 2000MHz$ ,  $P_{OUT} = 0dBm/$ tone for single tone and two tone tests, OIP3 tone delta = 1MHz, all RF source and RF load impedances =  $50\Omega$ , PCB board and connector losses are de-embedded, unless otherwise noted.

Parameter	Symbol	Condition	Minimum	Typical	Maximum	Units
Input Return Loss	RL <sub>AMPIN</sub>			16		dB
Output Return Loss	RL <sub>AMPOUT</sub>			17		dB
Gain	G <sub>LB</sub>	400MHz Low Band Bias		11.1		dB
		900MHz Low Band Bias	<b>12.1</b> [a]	13.2	<b>14.2</b>	
	G <sub>MB</sub>	2000MHz Mid Band Bias		14.1		
	G <sub>HB</sub>	2700MHz High Band Bias	<b>13.0</b>	14.4	<b>15.5</b>	
	G <sub>WB</sub>	400MHz Wide Band Bias		11.1		
		2700MHz Wide Band Bias		14.4		
Noise Figure	NF <sub>LB</sub>	400MHz Low Band Bias		4.5		dB
		900MHz Low Band Bias		4.3		
	NF <sub>MB</sub>	2000MHz Mid Band Bias		4.5		
	NF <sub>HB</sub>	2700MHz High Band Bias		5.0		
	NF <sub>WB</sub>	400MHz Wide Band Bias		4.5		
		2700MHz Wide Band Bias		5.0		
Output Third Order Intercept Point	OIP3 <sub>LB</sub>	400MHz Low Band Bias		37		dBm
		900MHz Low Band Bias	38 [b]	41.5		
	OIP3 <sub>MB</sub>	2000MHz Mid Band Bias		41		
	OIP3 <sub>HB</sub>	2700MHz High Band Bias		40		
	OIP3 <sub>WB</sub>	400MHz Wide Band Bias		35		
		2700MHz Wide Band Bias		39		
Output 1dB Compression	OP1dB <sub>LB</sub>	400MHz Low Band Bias		19.5		dBm
		900MHz Low Band Bias		20.9		
	OP1dB <sub>MB</sub>	2000MHz Mid Band Bias		19.7		
	OP1dB <sub>HB</sub>	2700MHz High Band Bias		19.5		
	OP1dB <sub>WB</sub>	400MHz Wide Band Bias		18.7		
		2700MHz Wide Band Bias		19.5		
Reverse Isolation	RevISO <sub>LB</sub>	400MHz Low Band Bias		20.5		dB
		900MHz Low Band Bias		18.5		
	RevISO <sub>MB</sub>	2000MHz Mid Band Bias		18		
	RevISO <sub>HB</sub>	2700MHz High Band Bias		18		
	RevISO <sub>WB</sub>	400MHz Low Band Bias		20.5		
		2700MHz High Band Bias		18		

a. Items in min/max columns in **bold italics** are guaranteed by test.

b. Items in min/max columns that are not bold/italics are guaranteed by design characterization.



**Table 6. Stand Alone Voltage Variable Attenuator Electrical Characteristics**

Typical Application Circuit.  $V_{CC} = +5V$ ,  $T_{EP} = +25^{\circ}C$ , signals applied to ATTEN\_RF1 input,  $f_{RF} = 2000MHz$ , minimum attenuation,  $P_{IN} = 0dBm$  for small signal parameters,  $P_{IN} = +20dBm$  / tone for single tone and two tone linearity tests, two tone delta frequency = 50MHz, all RF source and RF load impedances =  $50\Omega$ , PCB board traces and connector losses are de-embedded, unless otherwise noted.

Parameter	Symbol	Condition	Minimum	Typical	Maximum	Units
Insertion Loss	$A_{min}$	50MHz [a]		1.0		dB
		700MHz		1.2		
		2000MHz		1.4	<b>1.9</b>	
		2700MHz		1.5		
		6000MHz		2.7		
Maximum Attenuation	$A_{max}$	50MHz [a]		29		dB
		700MHz		35.6		
		2000MHz	33.2	35.5		
		2700MHz		35.4		
		6000MHz		37		
Relative Insertion Phase Relative to Insertion Loss	$\Phi_{\Delta MAX}$	At 35dB attenuation		27		deg
	$\Phi_{\Delta MID}$	At 18dB attenuation		10		
Minimum ATTEN_RF1 Return Loss Over Control Voltage Range	S11	50MHz [a]		16		dB
		700MHz		17		
		2000MHz		17		
		2700MHz		17		
		6000MHz		15		
Minimum ATTEN_RF2 Return Loss Over Control Voltage Range	S22	50MHz [a]		14		dB
		700MHz		15		
		2000MHz		16		
		2700MHz		17		
		6000MHz		13		
Input IP3	IIP3			65		dBm
	IIP3 <sub>ATTEN</sub>	All attenuation settings	44	47		dBm
Minimum Output IP3	OIP3 <sub>MIN</sub>	Maximum attenuation		35		dBm
Input IP2 ( $f_1 + f_2$ )	IIP2	$P_{IN} + IM2$ [dBc]		95		dBm
	IIP2 <sub>MIN</sub>	All attenuation settings		87		
Input IH2	HD2	$P_{IN} + H2$ [dBc]		90		dBm
Input IH3	HD3	$P_{IN} + H3$ [dBc]/2		54		dBm
Input 1dB Compression [b]	IP1dB			34.4		dBm
Settling Time	$T_{SETTL0.1dB}$	Any 1dB step in the 0dB to 33dB range. 50% $V_{CTRL}$ to RF settled to within $\pm 0.1dB$		15		$\mu s$

a. Set blocking capacitors C2 and C9 to 0.01 $\mu F$  to achieve best return loss performance at 50MHz.

b. The input 1dB compression point is a linearity figure of merit. Refer to Absolute Maximum Ratings section for the maximum RF input power.

## Thermal Characteristics

**Table 7. Package Thermal Characteristics**

Parameter	Symbol	Value	Units
Amplifier - Junction to Ambient Thermal Resistance.	$\theta_{JA-AMP}$	40	°C/W
Attenuator - Junction to Ambient Thermal Resistance.	$\theta_{JA-ATTN}$	80	°C/W
Amplifier - Junction to Case Thermal Resistance. (Case is defined as the exposed paddle)	$\theta_{JC\_BOT\_AMP}$	4	°C/W
Attenuator - Junction to Case Thermal Resistance. (Case is defined as the exposed paddle)	$\theta_{JC\_BOT\_ATTN}$	5	°C/W
Moisture Sensitivity Rating (Per J-STD-020)		MSL 1	

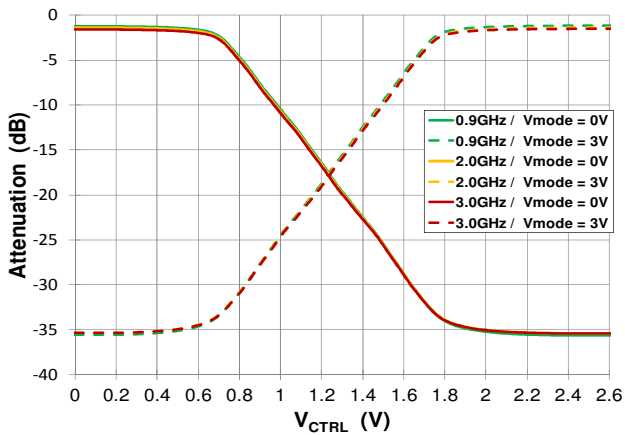
## Typical Operating Conditions (TOC)

Unless otherwise noted:

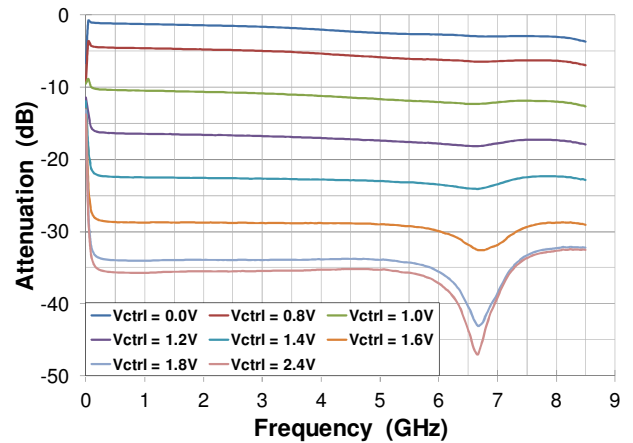
- $V_{CC} = +5.0V$
- $T_{EP} = +25^{\circ}C$  ( $T_{EP}$  is defined as the exposed paddle temperature).
- Amplifier components configured for operation per Table 8 for each indicated band.
- $P_{OUT} = 0dBm/tone$  for all amplifier linearity tests.
- 1MHz tone spacing for all amplifier linearity tests.
- $P_{IN} = +20dBm/tone$  applied to ATTN\_RF1 for all attenuator linearity tests.
- 50MHz tone spacing for all attenuator linearity tests.
- $V_{CTRL}$  setting = minimum attenuation setting.
- STBY = Logic HIGH (or open).
- Band Select = GND.
- $V_{MODE} = Logic\ LOW = Negative\ Slope$ .
- Evaluation kit trace and connector losses are fully de-embedded.
- S-parameters for the amplifier and attenuator have external RF caps replaced by  $0\Omega$  resistors for purposes of displaying broadband results.
- Since the Wide Band and Mid Band settings are the same in Table 8, the Mid Band results will be the same curves as those displayed in the Amplifier Wide Band section.

## Typical Performance Characteristics – Attenuator [1]

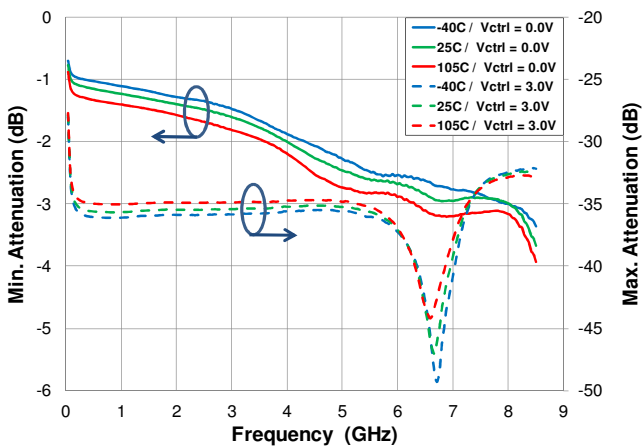
**Figure 4. Attenuation vs.  $V_{CTRL}$  over Frequency and  $V_{MODE}$**



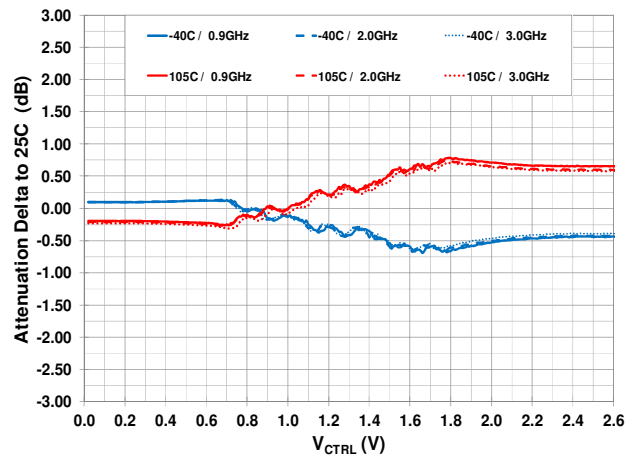
**Figure 5. Attenuation vs. Frequency over  $V_{CTRL}$**



**Figure 6. Min. and Max. Attenuation vs. Frequency over Temperature**

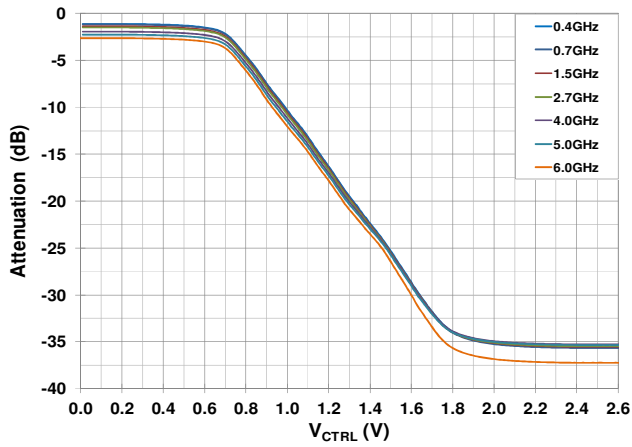


**Figure 7. Attenuation Delta to +25 C vs.  $V_{CTRL}$  over Frequency and Temperature**

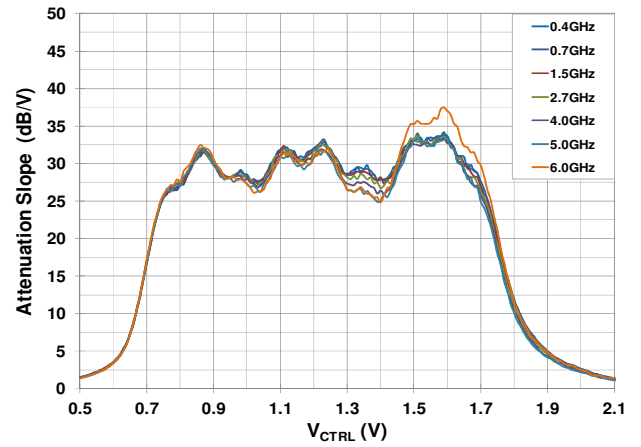


## Typical Performance Characteristics – Attenuator [2]

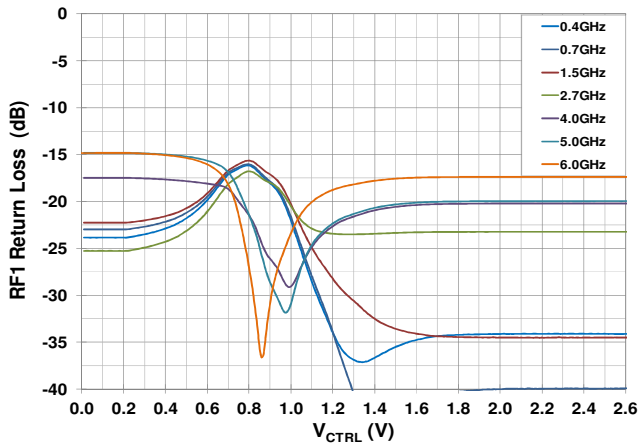
**Figure 8. Attenuation vs.  $V_{CTRL}$  over Frequency**



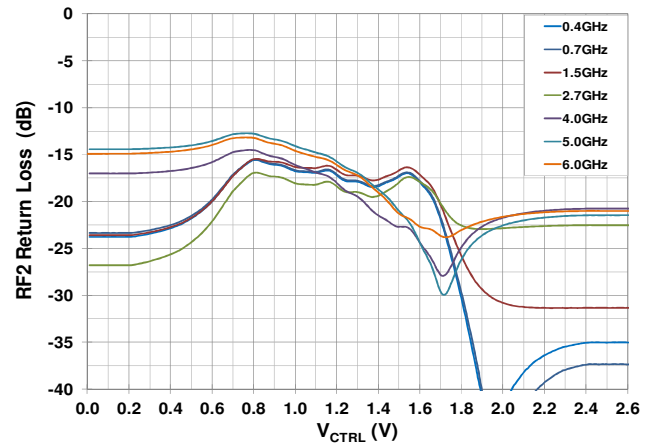
**Figure 9. Attenuation Slope vs.  $V_{CTRL}$  over Frequency**



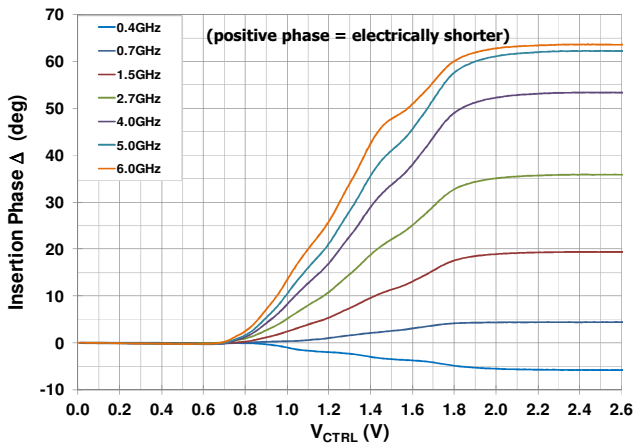
**Figure 10. Return Loss (ATTEN\_RF1 port) vs.  $V_{CTRL}$  over Frequency**



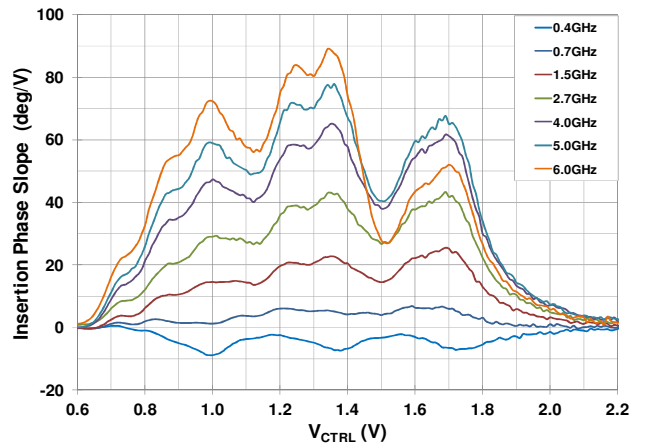
**Figure 11. Return Loss (ATTEN\_RF2 port) vs.  $V_{CTRL}$  over Frequency**



**Figure 12. Insertion Phase Change vs.  $V_{CTRL}$  over Frequency**

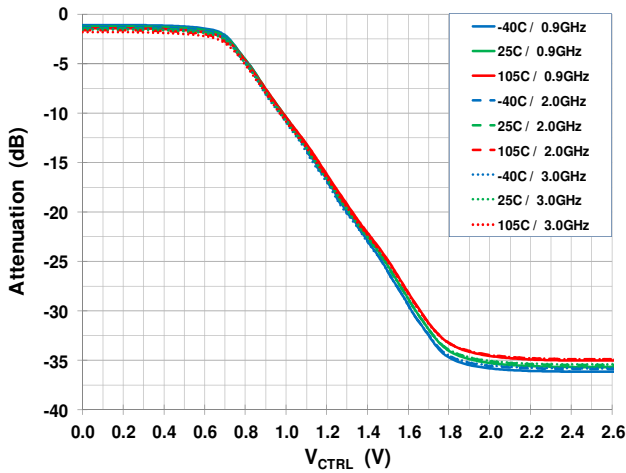


**Figure 13. Insertion Phase Slope vs.  $V_{CTRL}$  over Frequency**

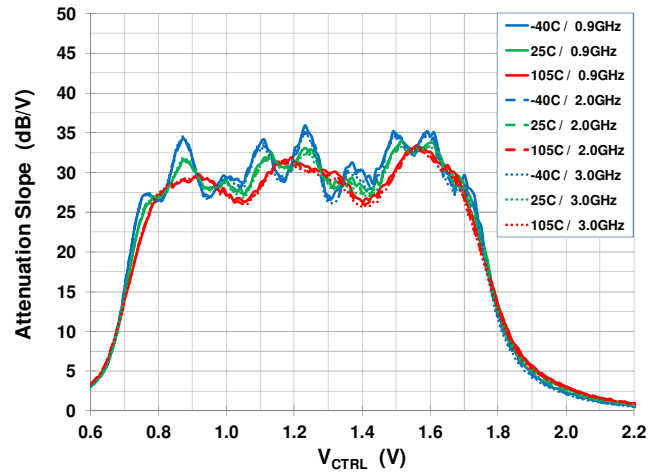


## Typical Performance Characteristics – Attenuator [3]

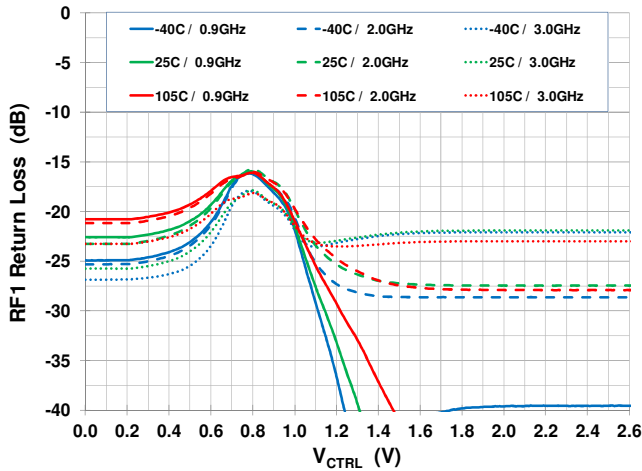
**Figure 14. Attenuation Response vs.  $V_{CTRL}$  over Frequency and Temperature**



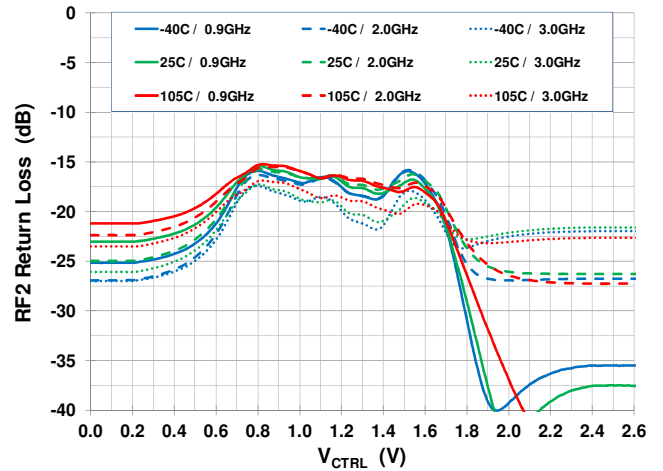
**Figure 15. Attenuation Slope vs.  $V_{CTRL}$  over Frequency and Temperature**



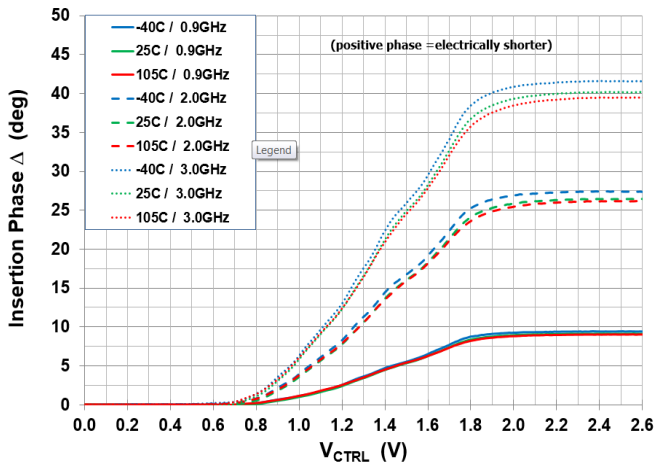
**Figure 16. Return Loss (ATTEN\_RF1) vs.  $V_{CTRL}$  over Frequency and Temperature**



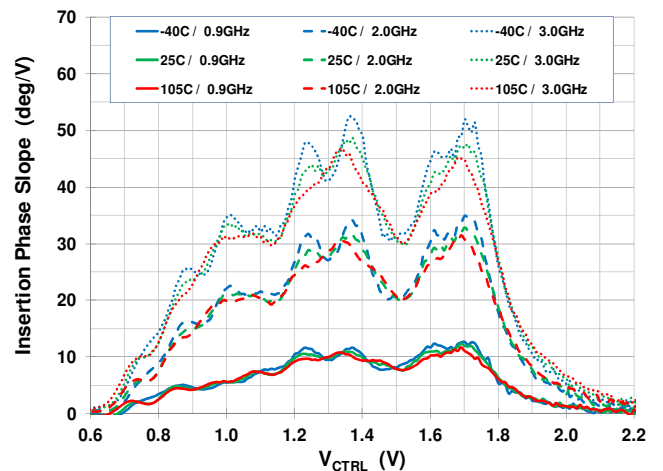
**Figure 17. Return Loss (ATTEN\_RF2) vs.  $V_{CTRL}$  over Frequency and Temperature**



**Figure 18. Insertion Phase Change vs.  $V_{CTRL}$  over Frequency and Temperature**

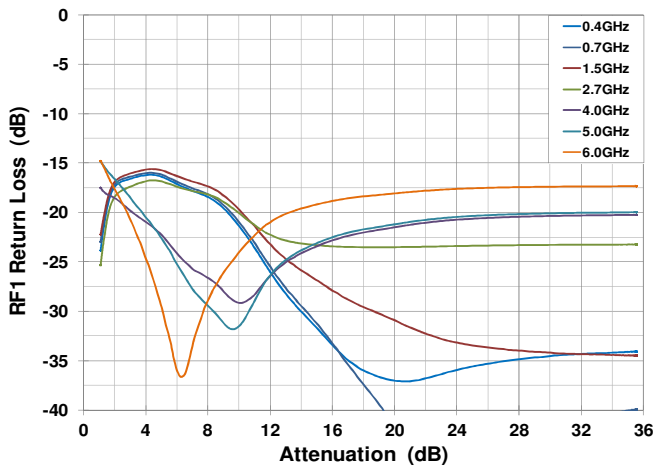


**Figure 19. Insertion Phase Slope vs.  $V_{CTRL}$  over Frequency and Temperature**

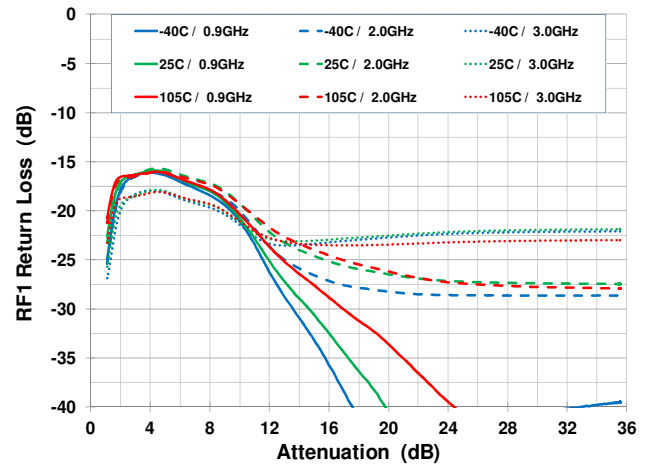


## Typical Performance Characteristics – Attenuator [4]

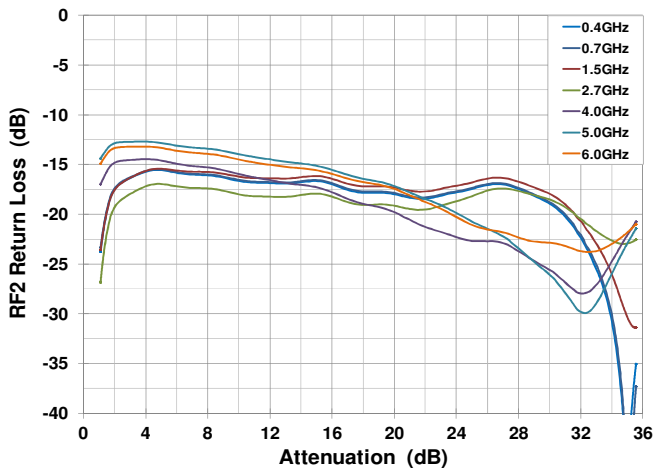
**Figure 20. Return Loss (ATTEN\_RF1 port) vs. Attenuation over Frequency**



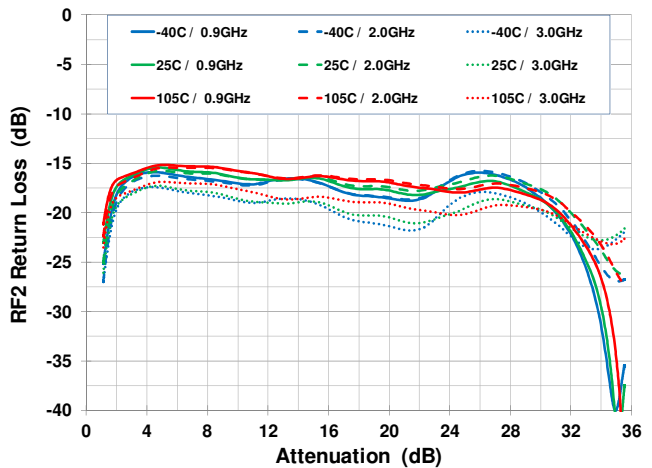
**Figure 21. Return Loss (ATTEN\_RF1 port) vs. Attenuation over Freq & Temp**



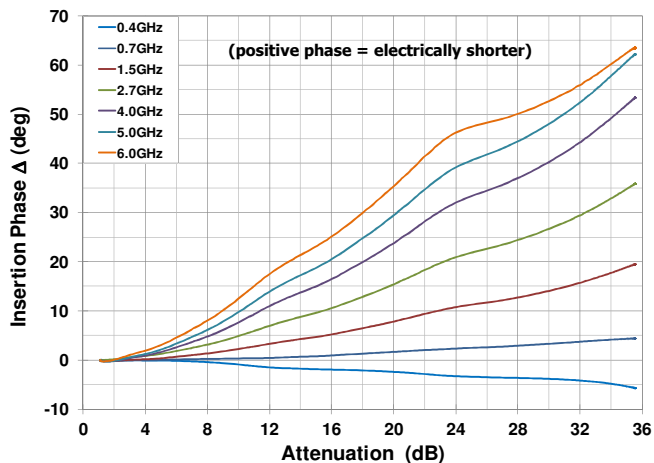
**Figure 22. Return Loss (ATTEN\_RF2 port) vs. Attenuation over Frequency**



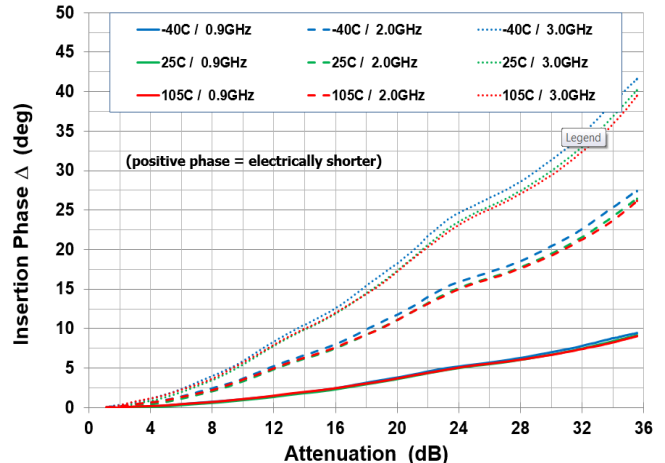
**Figure 23. Return Loss (ATTEN\_RF2 port) vs. Attenuation over Freq & Temp**



**Figure 24. Insertion Phase Change vs. Attenuation over Frequency**

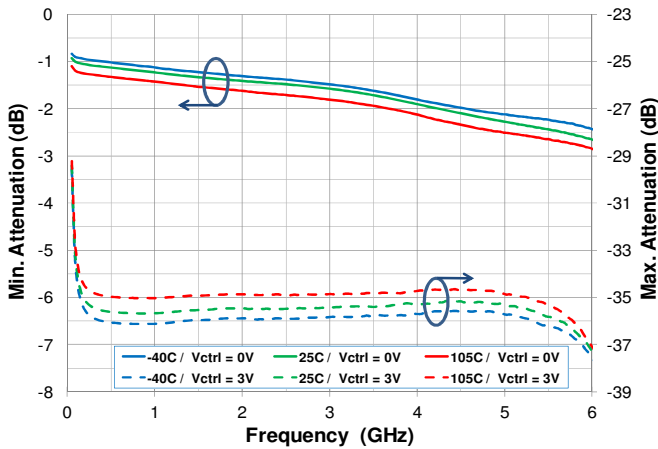


**Figure 25. Insertion Phase Change vs. Attenuation over Freq & Temp**

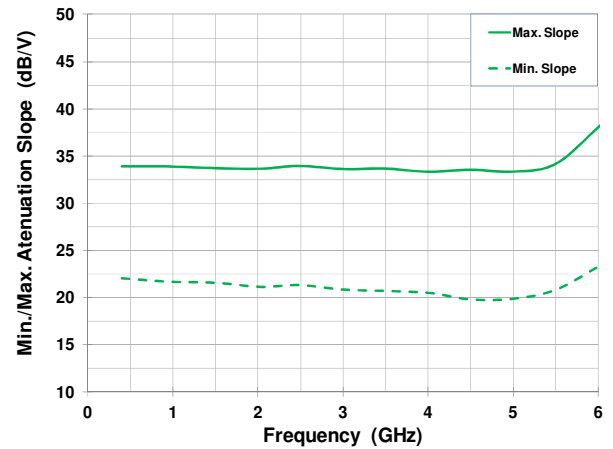


## Typical Performance Characteristics – Attenuator [5]

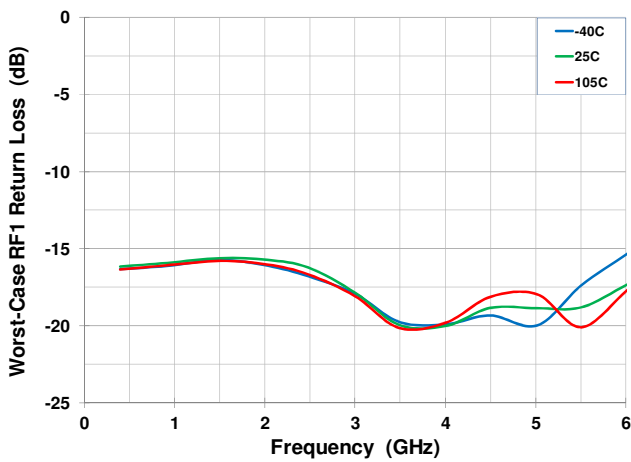
**Figure 26. Min. and Max. Attenuation vs. Frequency**



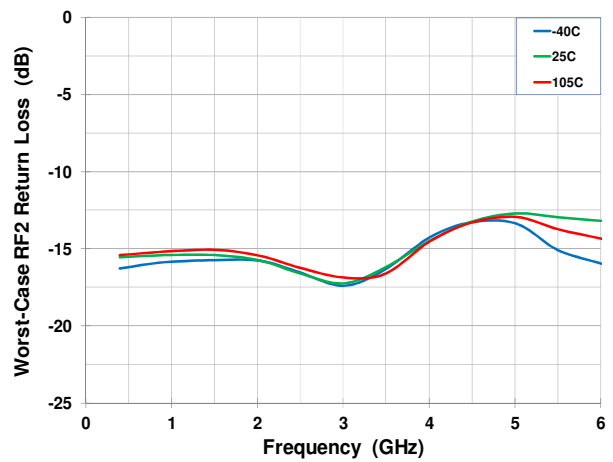
**Figure 27. Min. and Max. Attenuation Slope vs. Frequency**



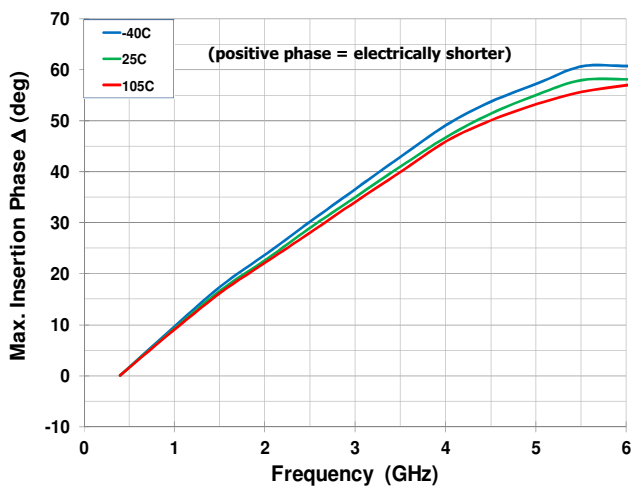
**Figure 28. Worst-Case Return Loss (ATTEN\_RF1 port) vs. Frequency over Temp**



**Figure 29. Worst-Case Return Loss (ATTEN\_RF2 port) vs. Frequency over Temp**

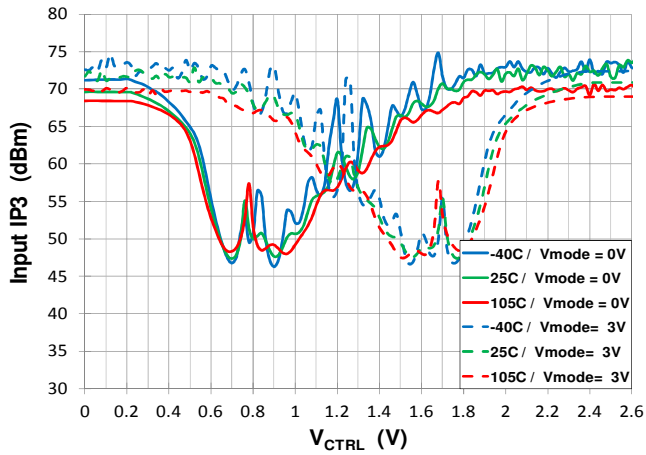


**Figure 30. Max. Insertion Phase Change vs. Frequency over Temp**

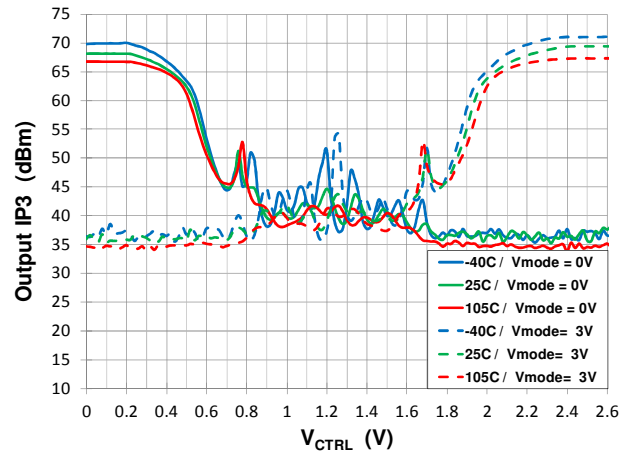


## Typical Performance Characteristics – 2 GHz Attenuator [6]

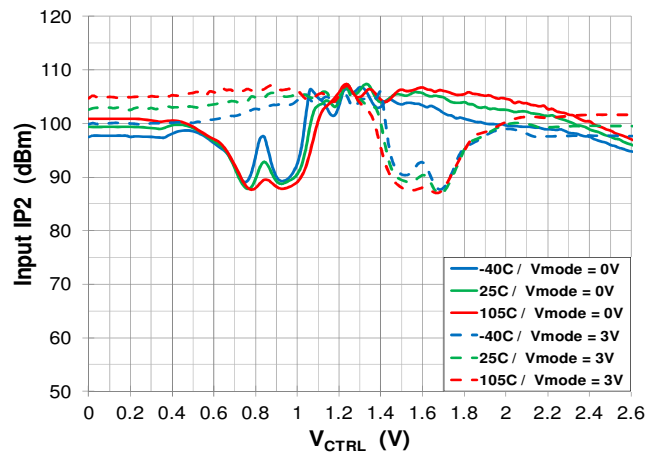
**Figure 31. Input IP3 vs.  $V_{CTRL}$  over  $V_{MODE}$  and Temperature**



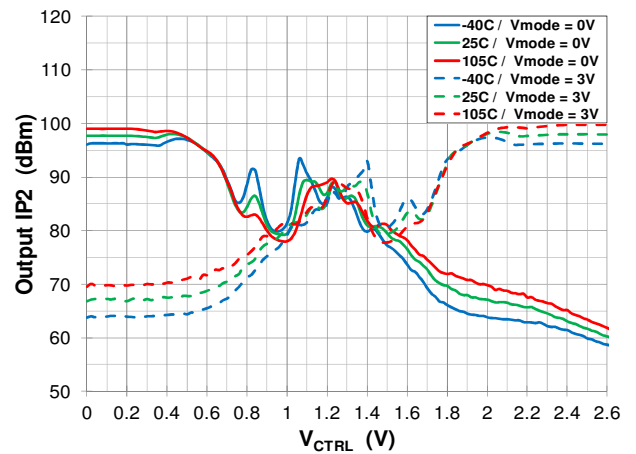
**Figure 32. Output IP3 vs.  $V_{CTRL}$  over  $V_{MODE}$  and Temperature**



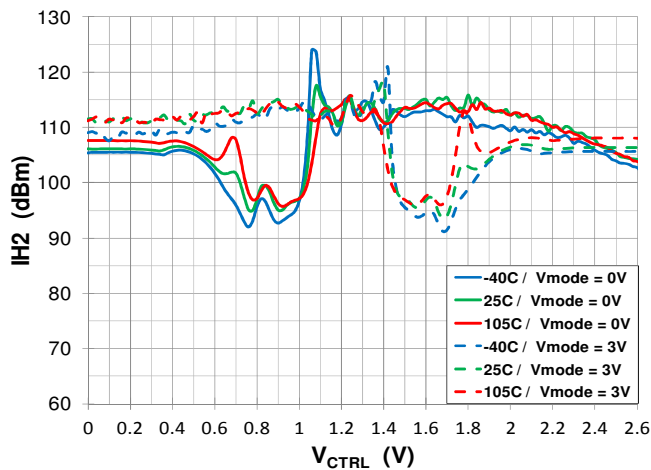
**Figure 33. Input IP2 vs.  $V_{CTRL}$  over  $V_{MODE}$  and Temperature**



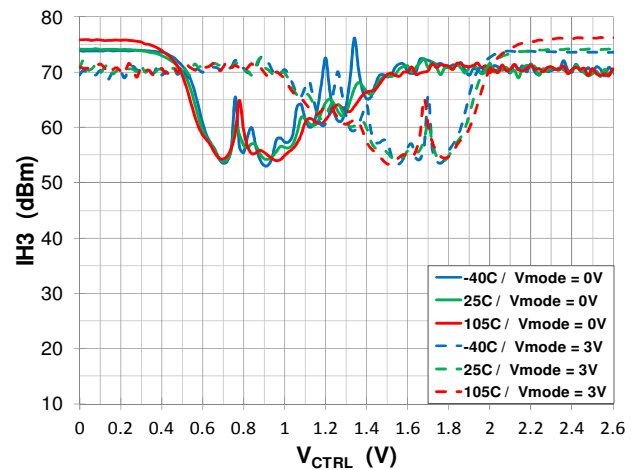
**Figure 34. Output IP2 vs.  $V_{CTRL}$  over  $V_{MODE}$  and Temperature**



**Figure 35. 2<sup>nd</sup> Harmonic Input Intercept Point vs.  $V_{CTRL}$  over  $V_{MODE}$  and Temperature**



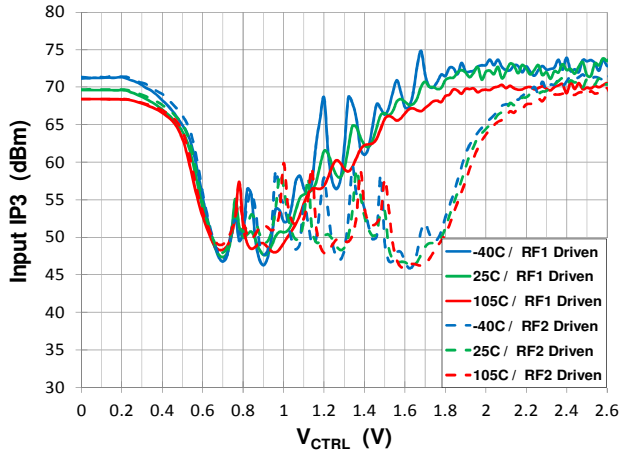
**Figure 36. 3<sup>rd</sup> Harmonic Input Intercept Point vs.  $V_{CTRL}$  over  $V_{MODE}$  and Temperature**



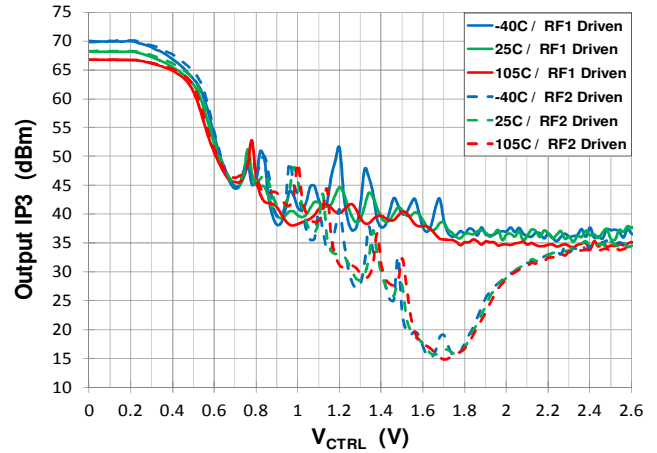


## Typical Performance Characteristics – 2 GHz Attenuator [7]

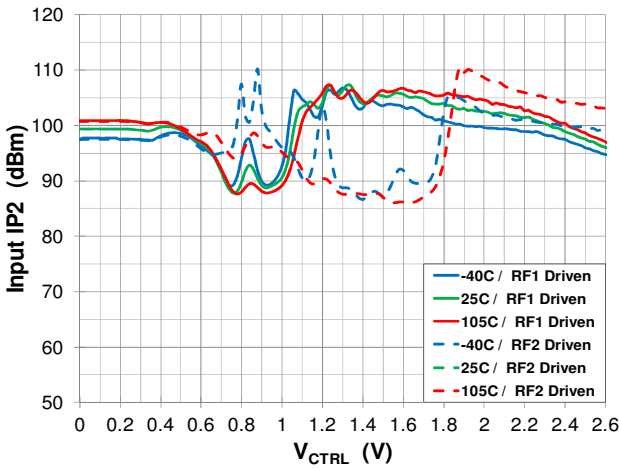
**Figure 37. Input IP3 vs.  $V_{CTRL}$  over RF Port and Temperature**



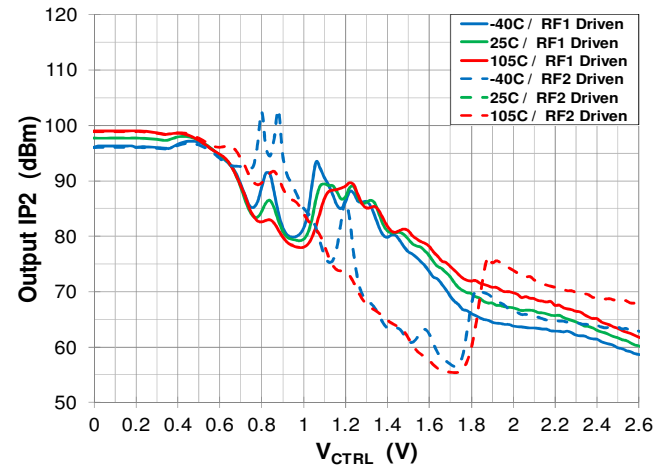
**Figure 38. Output IP3 vs.  $V_{CTRL}$  over RF Port and Temperature**



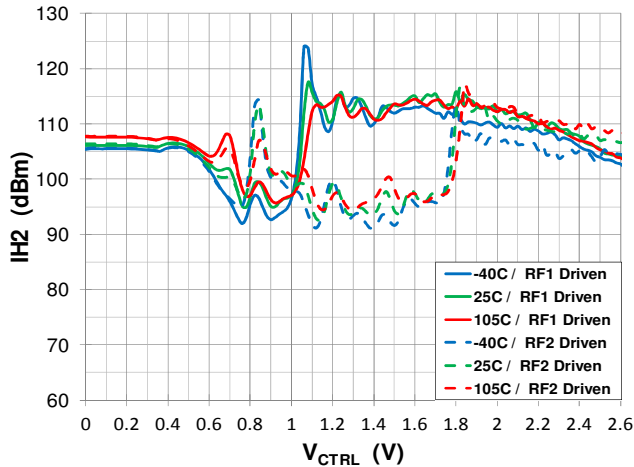
**Figure 39. Input IP2 vs.  $V_{CTRL}$  over RF Port and Temperature**



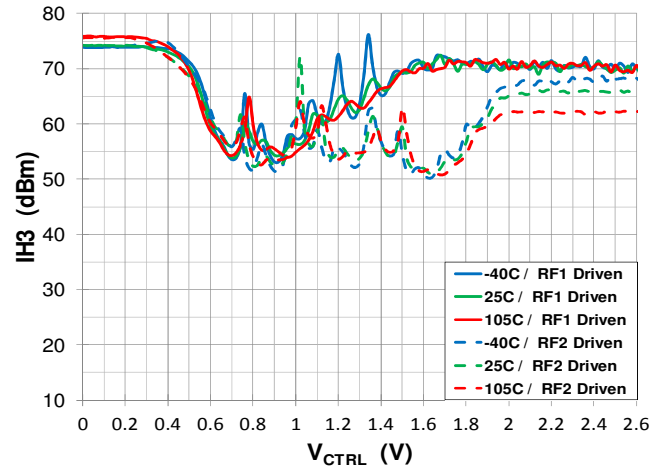
**Figure 40. Output IP2 vs.  $V_{CTRL}$  over RF Port and Temperature**



**Figure 41. 2<sup>nd</sup> Harm Input Intercept Point vs.  $V_{CTRL}$  over RF Port and Temp**

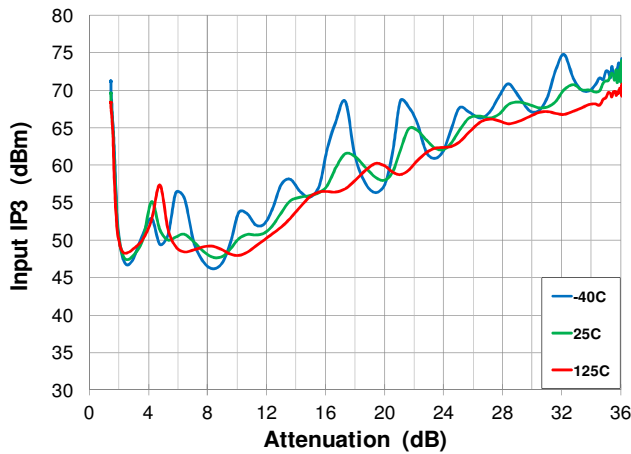


**Figure 42. 3<sup>rd</sup> Harm Input Intercept Point vs.  $V_{CTRL}$  over RF Port and Temp**

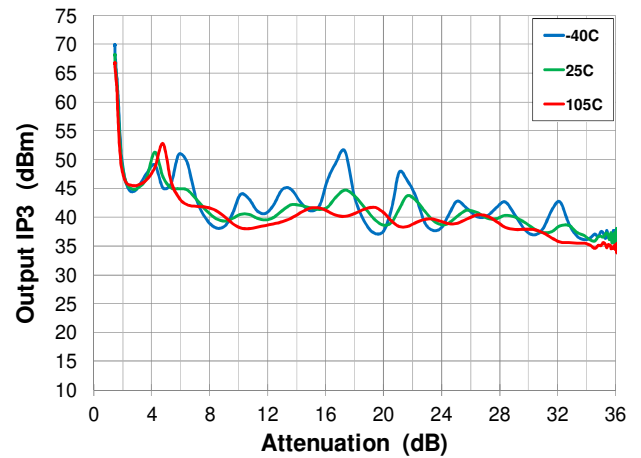


## Typical Performance Characteristics – 2 GHz Attenuator [8]

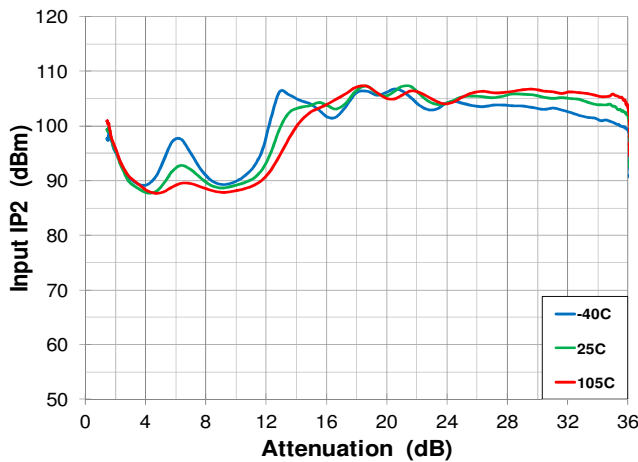
**Figure 43. Input IP3 vs. Attenuation over Temperature**



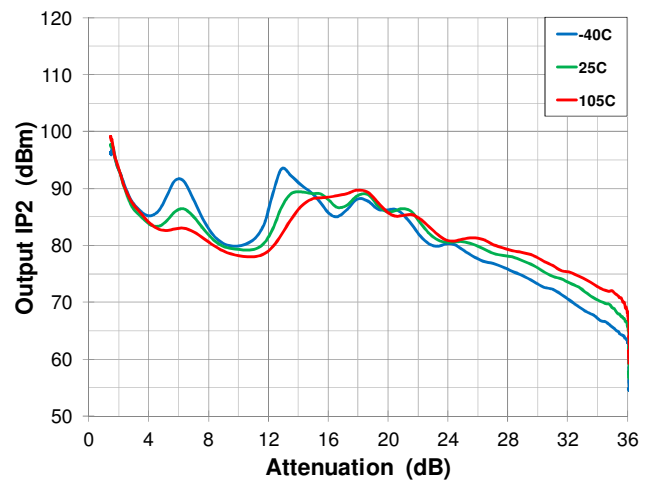
**Figure 44. Output IP3 vs. Attenuation over Temperature**



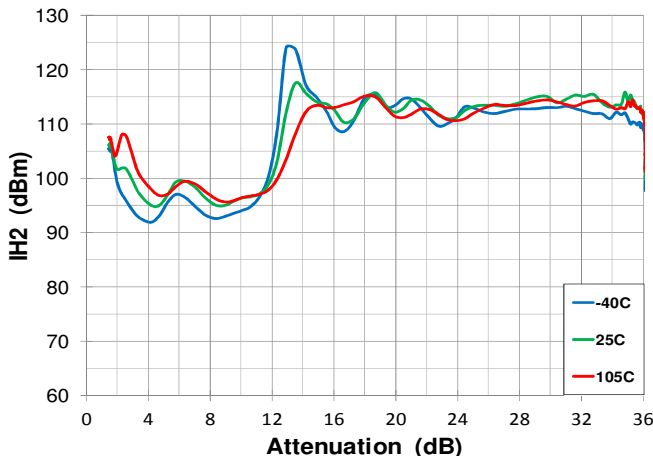
**Figure 45. Input IP2 vs. Attenuation over Temperature**



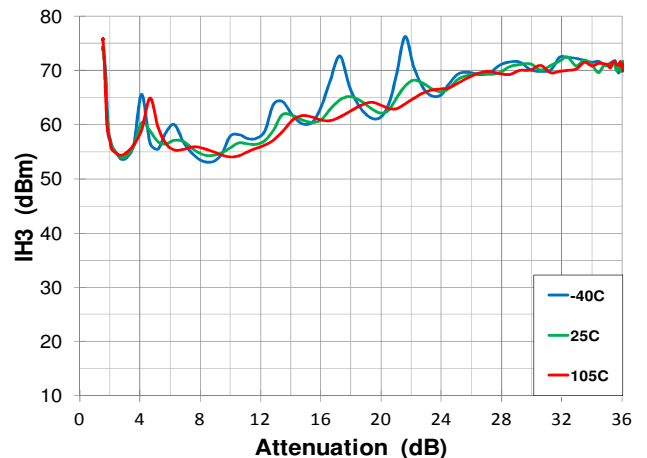
**Figure 46. Output IP2 vs. Attenuation over Temperature**



**Figure 47. 2<sup>nd</sup> Harm Input Intercept Point vs. Attenuation over Temperature**

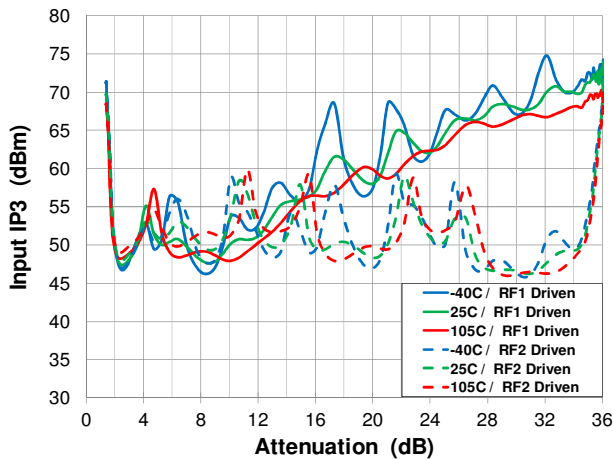


**Figure 48. 3<sup>rd</sup> Harm Input Intercept Point vs. Attenuation over Temperature**

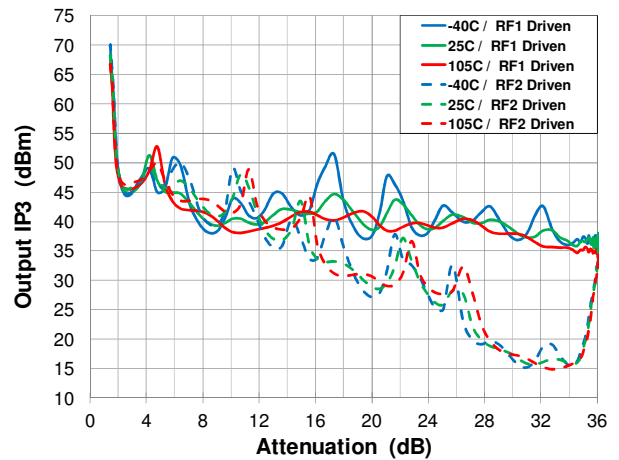


## Typical Performance Characteristics – 2 GHz Attenuator [9]

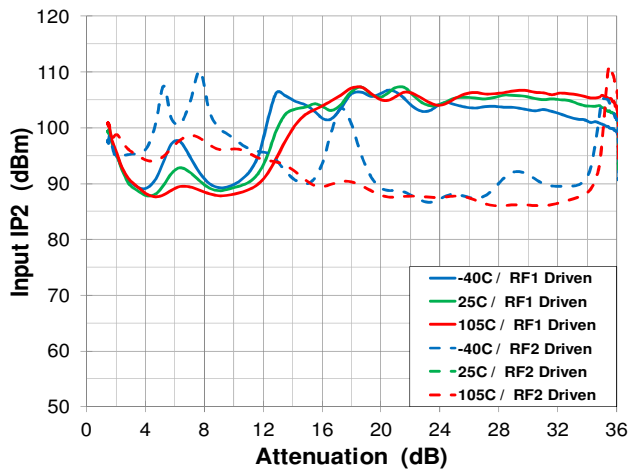
**Figure 49. Input IP3 vs. Attenuation over RF Port and Temperature**



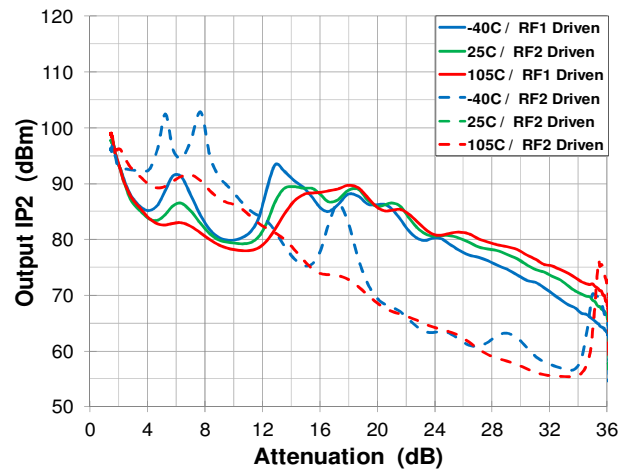
**Figure 50. Output IP3 vs. Attenuation over RF Port and Temperature**



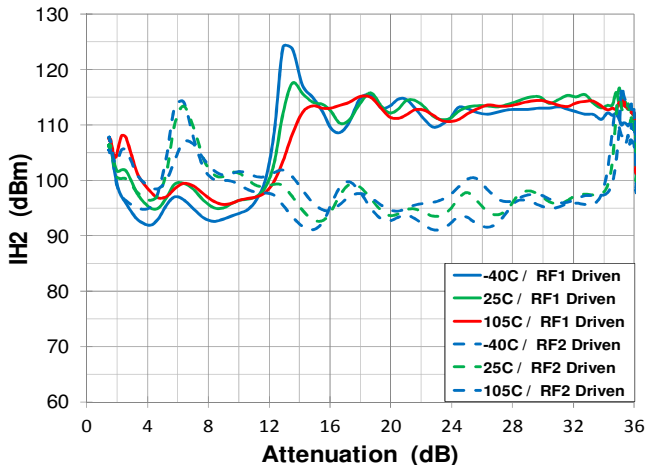
**Figure 51. Input IP2 vs. Attenuation over RF Port and Temperature**



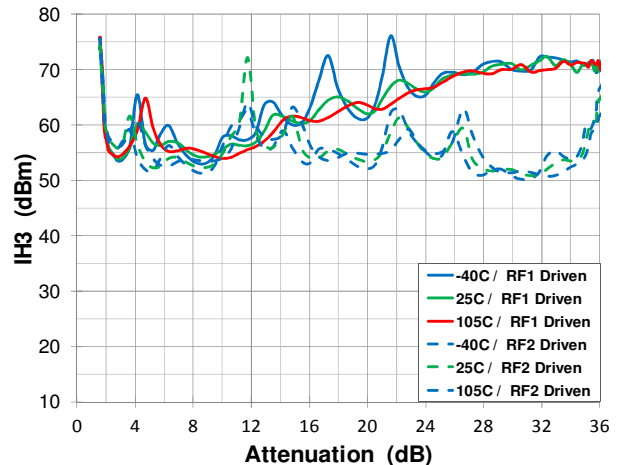
**Figure 52. Output IP2 vs. Attenuation over RF Port and Temperature**



**Figure 53. 2<sup>nd</sup> Harm Input Intercept Point vs. Attenuation over RF Port and Temp**

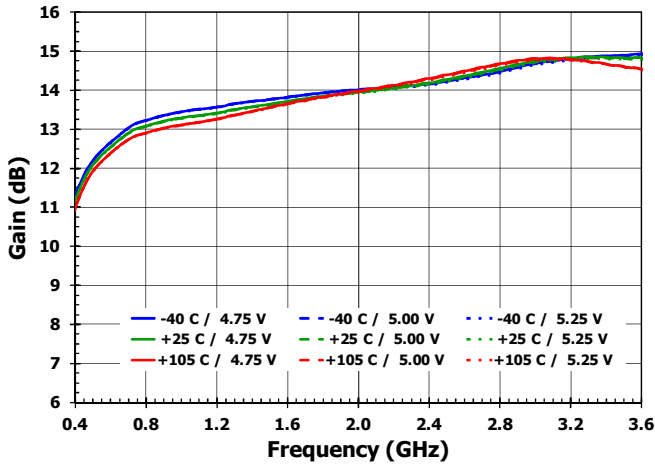


**Figure 54. 3<sup>rd</sup> Harm Input Intercept Point vs. Attenuation over RF Port and Temp**

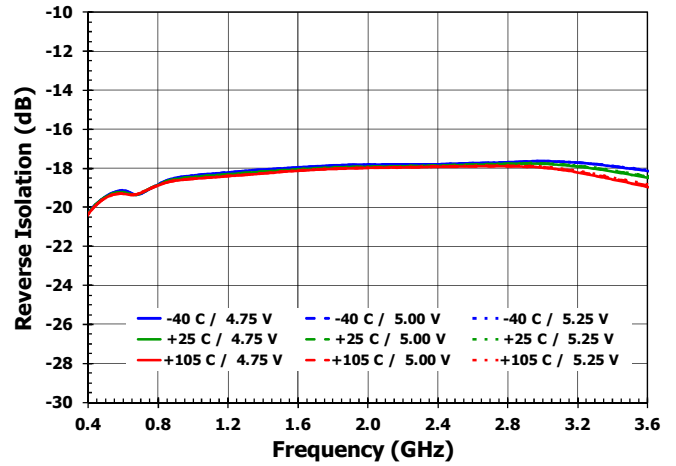


## Typical Performance Characteristics – Amplifier – Wide Band Mode [1]

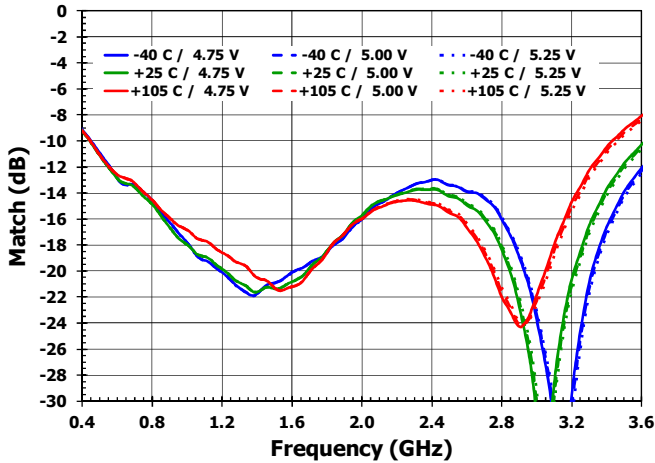
**Figure 55. Gain vs. Frequency over Temperature and Voltage – WB mode**



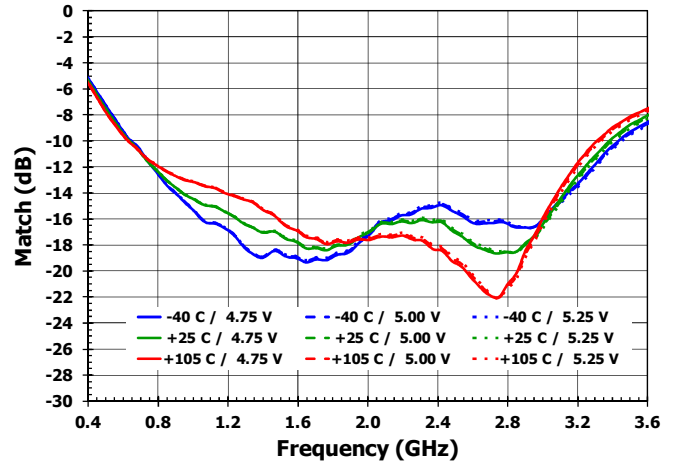
**Figure 56. Reverse Isolation vs. Frequency over Temperature and Voltage – WB Mode**



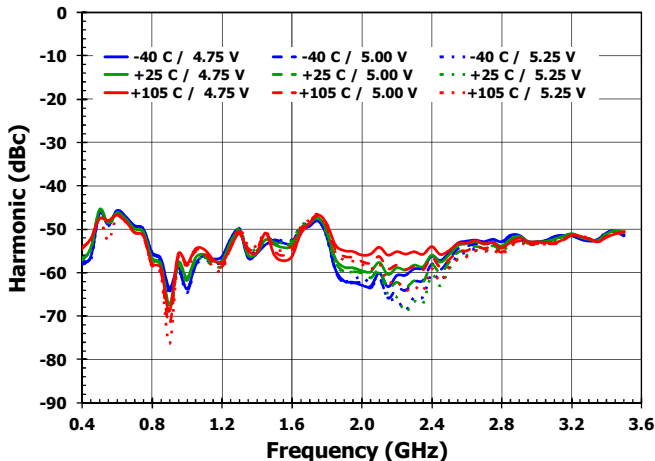
**Figure 57. Input Match vs. Frequency over Temperature and Voltage – WB Mode**



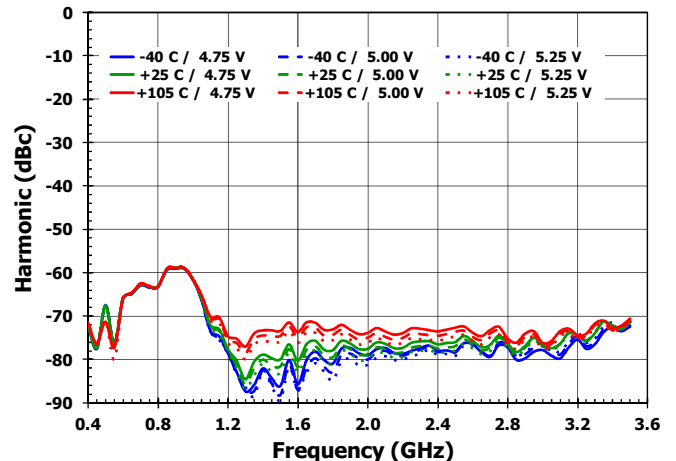
**Figure 58. Output Match vs. Frequency over Temperature and Voltage – WB Mode**



**Figure 59. 2<sup>nd</sup> Harmonic vs. Fundamental Freq over Temp and Voltage – WB Mode**

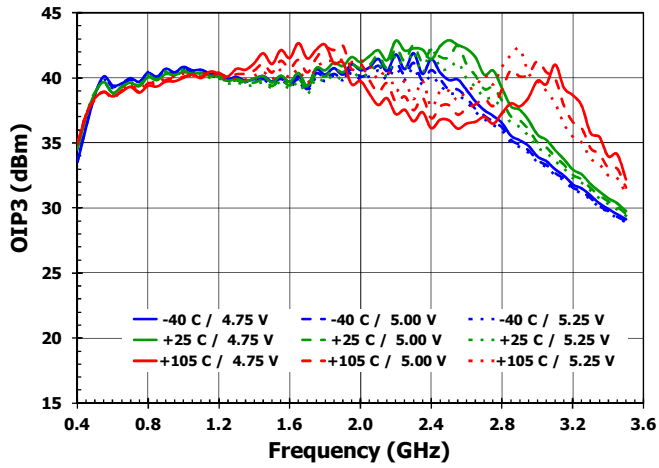


**Figure 60. 3<sup>rd</sup> Harmonic vs. Fundamental Freq over Temp and Voltage – WB Mode**

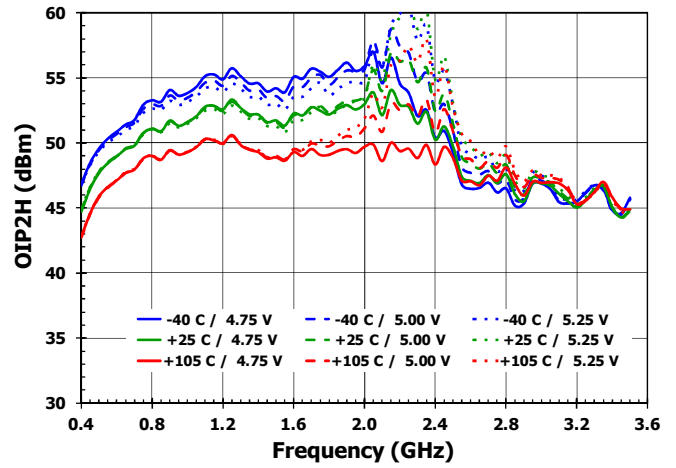


## Typical Performance Characteristics – Amplifier – Wide Band Mode [2]

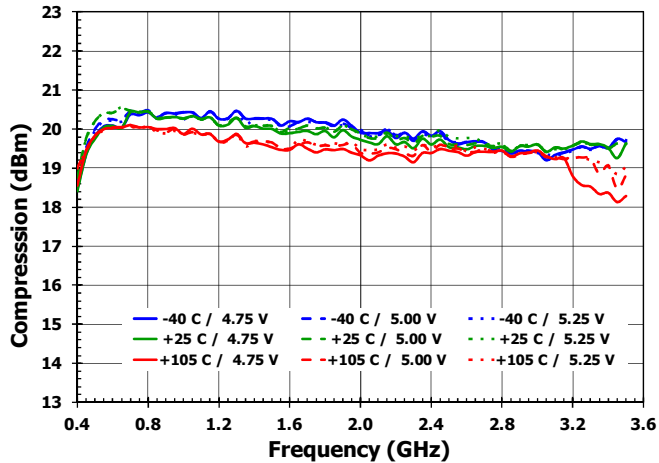
**Figure 61. Output IP3 vs. Frequency over Temperature and Voltage – WB Mode**



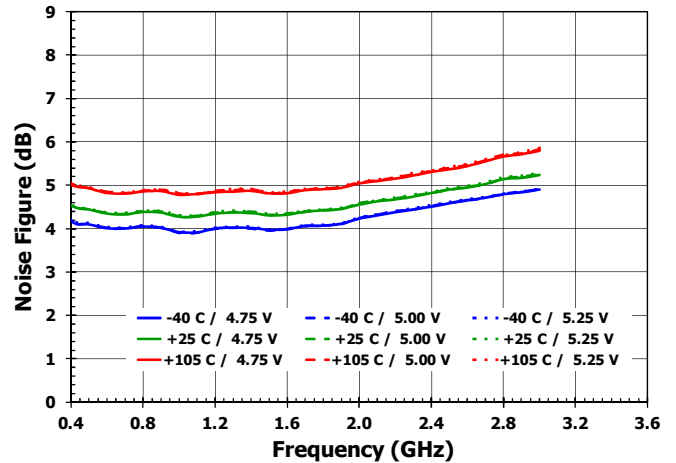
**Figure 62. Output IP2H vs. Frequency over Temperature and Voltage – WB Mode**



**Figure 63. Output P1dB vs. Frequency over Temperature and Voltage – WB Mode**

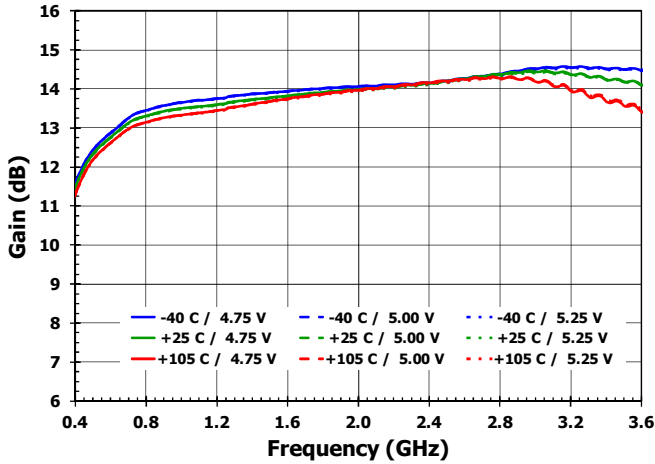


**Figure 64. Noise Figure vs. Frequency over Temperature and Voltage – WB Mode**

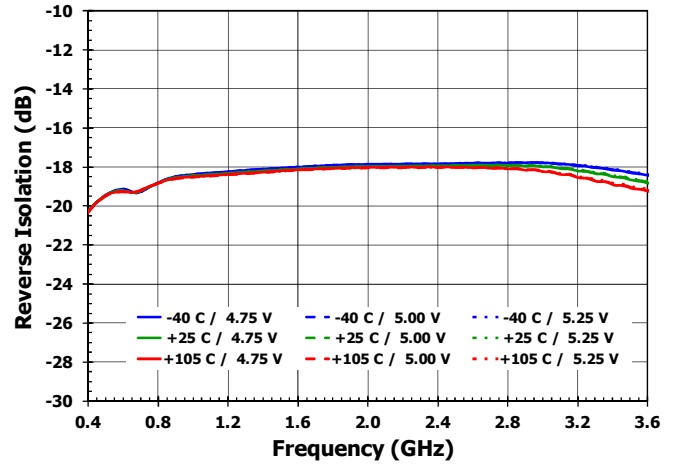


# Typical Performance Characteristics – Amplifier – Low Band Mode [1]

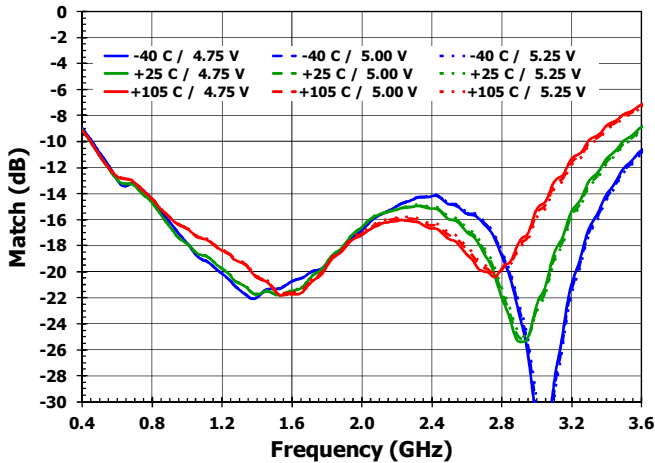
**Figure 65. Gain vs. Frequency over Temperature and Voltage – LB mode**



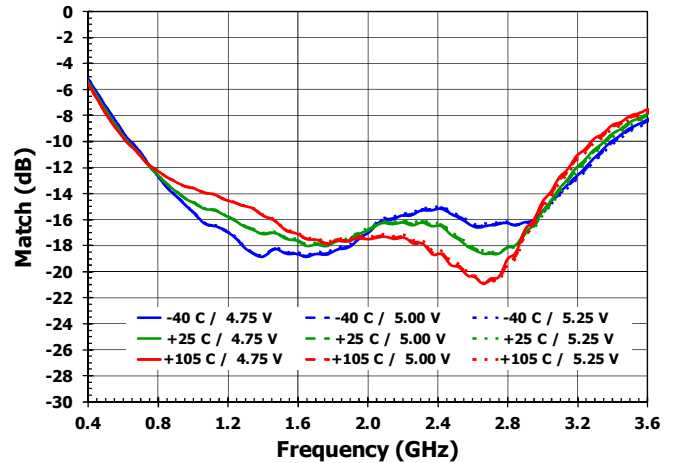
**Figure 66. Reverse Isolation vs. Frequency over Temperature and Voltage – LB Mode**



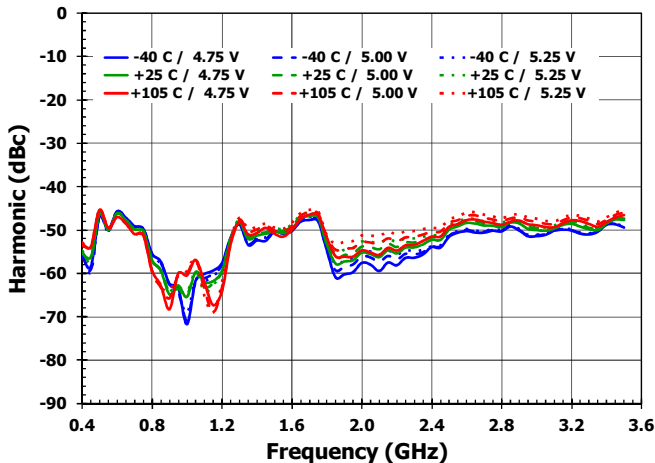
**Figure 67. Input Match vs. Frequency over Temperature and Voltage – LB Mode**



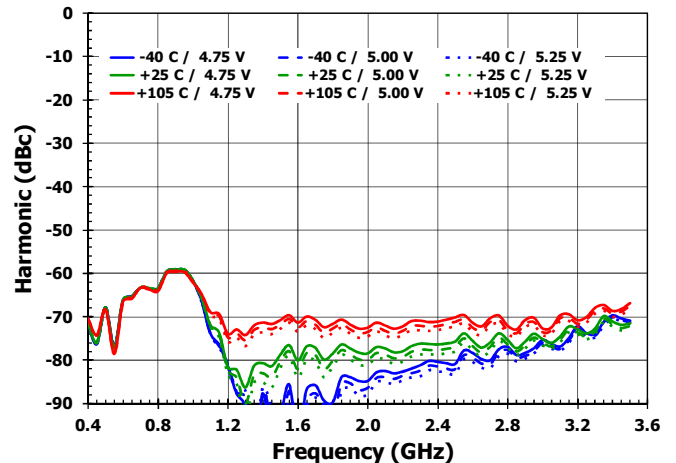
**Figure 68. Output Match vs. Frequency over Temperature and Voltage – LB Mode**



**Figure 69. 2<sup>nd</sup> Harmonic vs. Fundamental Freq over Temp and Voltage – LB Mode**

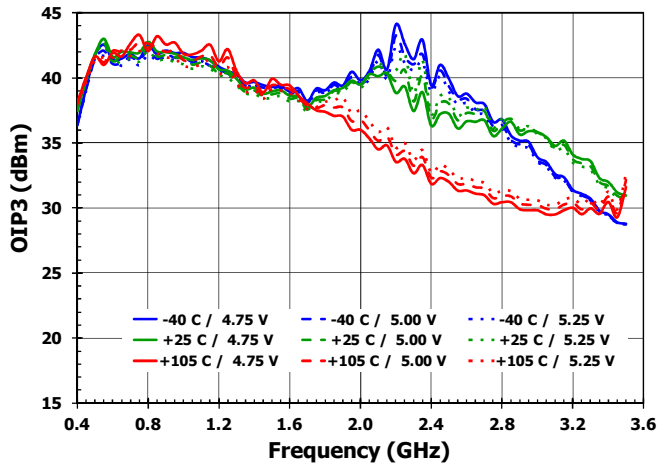


**Figure 70. 3<sup>rd</sup> Harmonic vs. Fundamental Freq over Temp and Voltage – LB Mode**

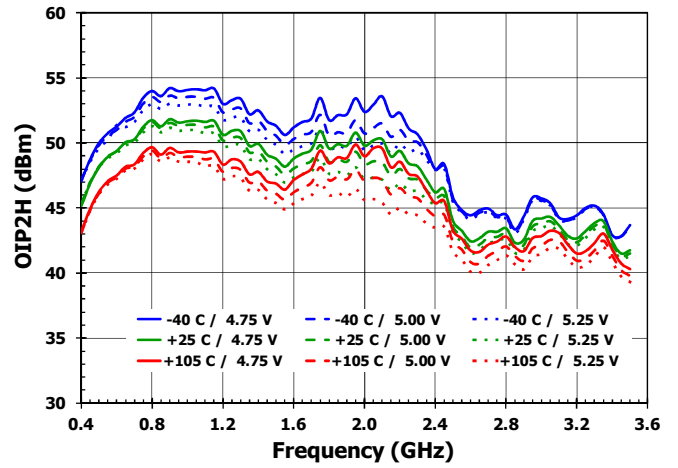


## Typical Performance Characteristics – Amplifier – Low Band Mode [2]

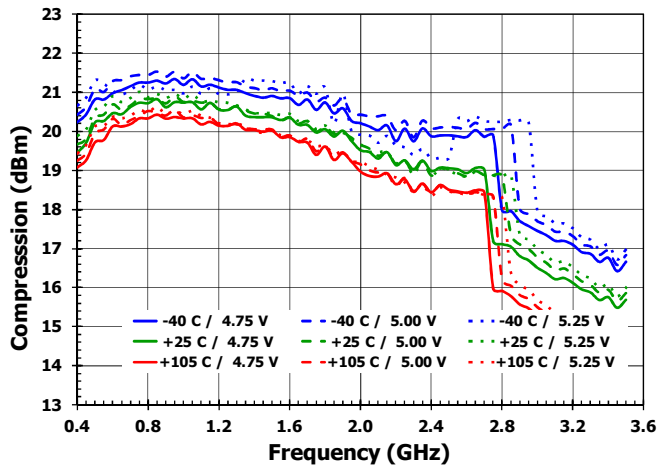
**Figure 71. Output IP3 vs. Frequency over Temperature and Voltage – LB Mode**



**Figure 72. Output IP2H vs. Frequency over Temperature and Voltage – LB Mode**

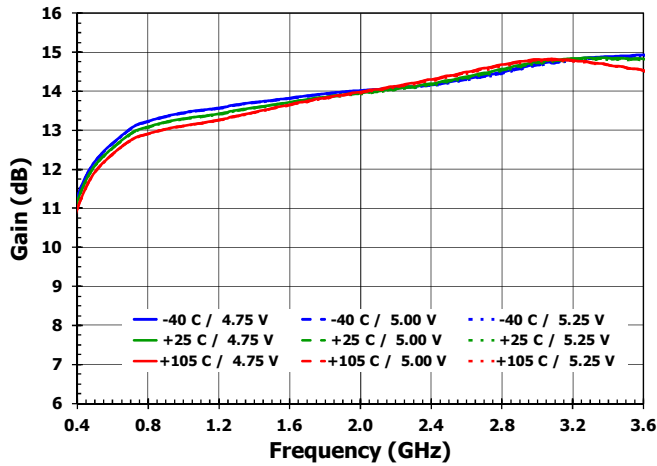


**Figure 73. Output P1dB vs. Frequency over Temperature and Voltage – LB Mode**

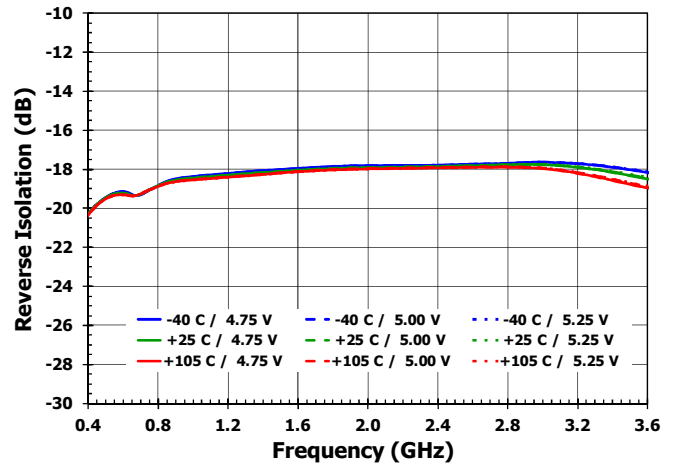


## Typical Performance Characteristics – Amplifier – High Band Mode [1]

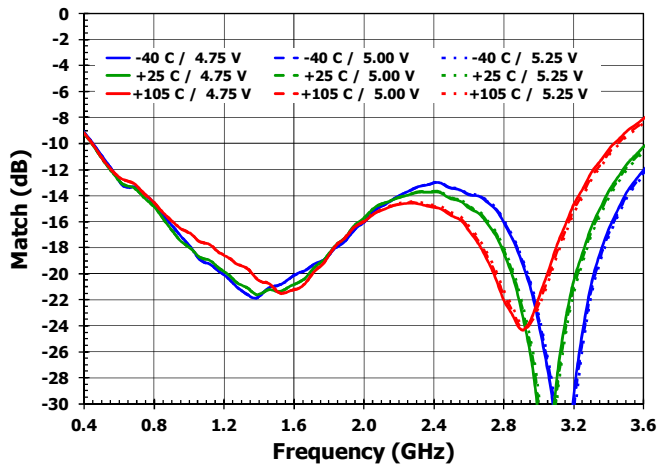
**Figure 74. Gain vs. Frequency over Temperature and Voltage – HB mode**



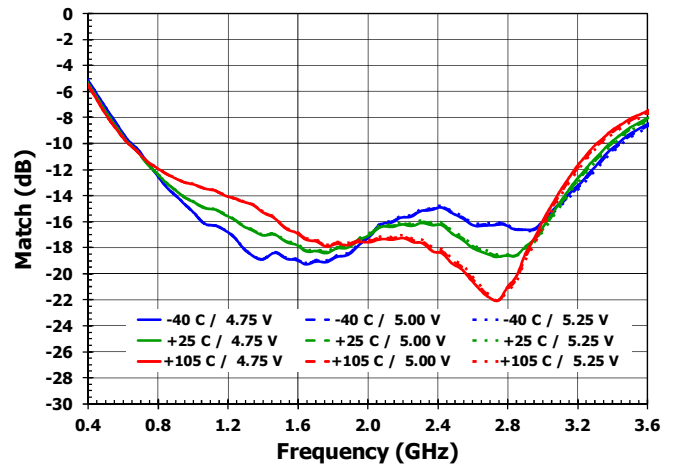
**Figure 75. Reverse Isolation vs. Frequency over Temperature and Voltage – HB Mode**



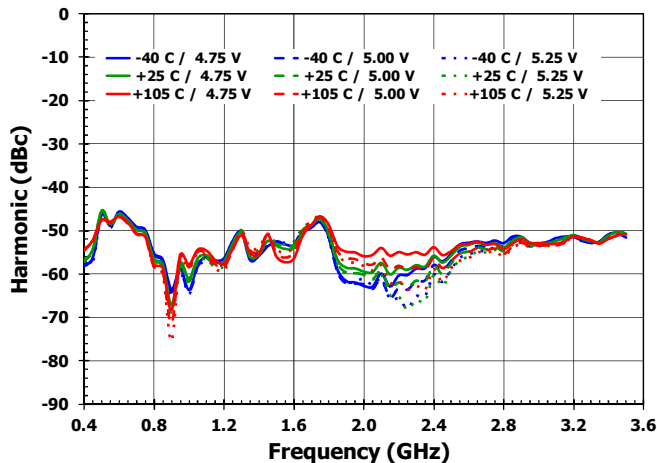
**Figure 76. Input Match vs. Frequency over Temperature and Voltage – HB Mode**



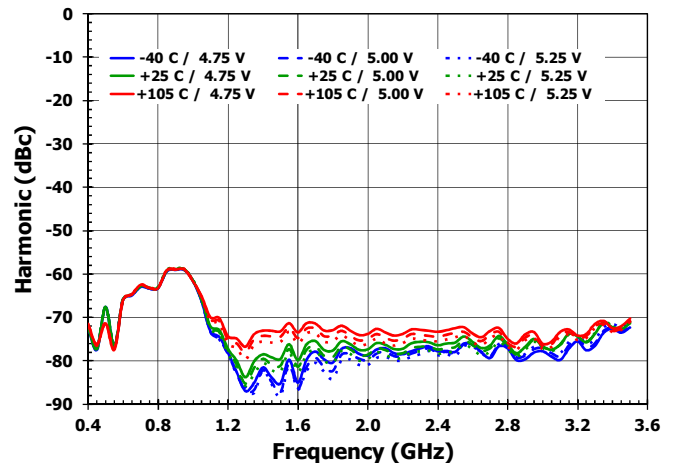
**Figure 77. Output Match vs. Frequency over Temperature and Voltage – HB Mode**



**Figure 78. 2<sup>nd</sup> Harmonic vs. Fundamental Freq over Temp and Voltage – HB Mode**



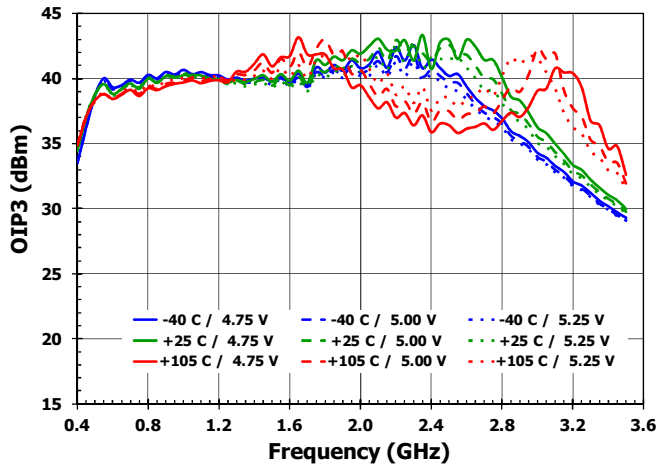
**Figure 79. 3<sup>rd</sup> Harmonic vs. Fundamental Freq over Temp and Voltage – HB Mode**



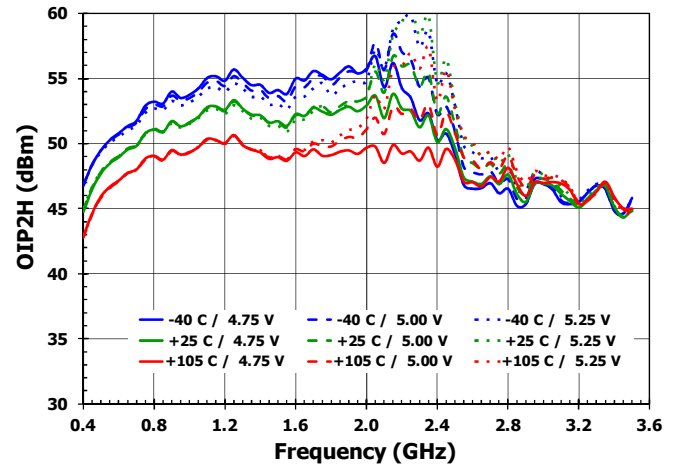


## Typical Performance Characteristics – Amplifier – High Band Mode [2]

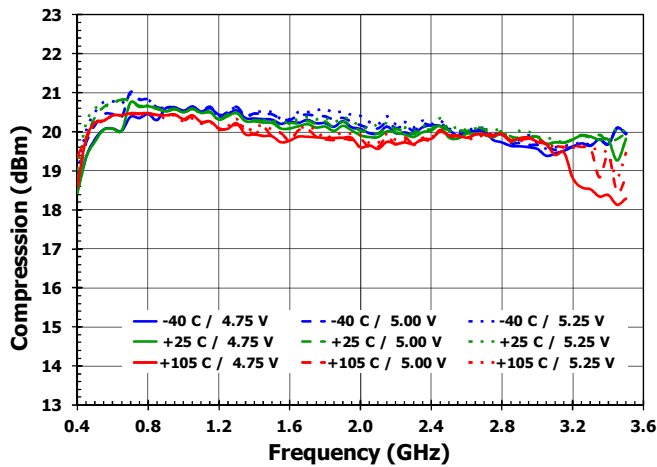
**Figure 80. Output IP3 vs. Frequency over Temperature and Voltage – HB Mode**



**Figure 81. Output IP2H vs. Frequency over Temperature and Voltage – HB Mode**



**Figure 82. Output P1dB vs. Frequency over Temperature and Voltage – HB Mode**



## Device Usage

**Table 8. Suggested Components for Optimum Linearity Performance of the Amplifier**

Band	Frequency Range (MHz)	Band_Select Pin 10	RSET Pin 12 to GND (k $\Omega$ )	RDSET Pin 13 to GND (k $\Omega$ )	C1 (pF)	I <sub>cc</sub> (mA)
Low Band	400 – 1100	LB (Open)	2.1	9.1	9	106
Mid Band	1100 – 2200	HB (GND)	2.4	60.4	9	121
High Band	2200 – 3000	HB (GND)	2.4	90.9	6	121
Wide Band	400 – 3000	HB (GND)	2.4	60.4	9	121

**Note:** Mid Band and Wide Band use the same setting and component values.

**Table 9. Control Pins Usage for the TX VGA**

Pin Description	Pin	Input Level	Function
Band_Select	10	Logic LOW	Improves higher frequency performance
		Logic HIGH or Open Circuit	Improves lower frequency performance
STBY	11	Logic LOW or Open Circuit	Amplifier Powered On
		Logic HIGH	Amplifier Power Savings Mode
V <sub>MODE</sub>	22	Logic LOW	Negative Attenuation Slope V <sub>CTRL</sub> = 0.0 V results in insertion loss V <sub>CTRL</sub> = 2.8 V results in maximum attenuation
		Logic HIGH	Positive Attenuation Slope V <sub>CTRL</sub> = 2.8 V results in insertion loss V <sub>CTRL</sub> = 0.0 V results in maximum attenuation

## Application Information

The F2480 has been optimized for use in high performance RF applications from 400 to 3000 MHz.

### STBY

The STBY control pin allows for power saving when the device is not in use. Setting the STBY pin as a logic low or by leaving the pin open will produce a full current operation mode. The STBY pin has an internal 1 M $\Omega$  resistor to ground. Applying logic high to this pin will put the part in the power savings mode.

### Band\_Select

The Band\_Select control pin can be used to boost the current in the device. This is typically done in the High Band and Wide Band frequency applications by grounding the Band\_Select pin. Internally there is a 1.5 M $\Omega$  pull-up resistor to set this pin high if no connection is made to it.

### RSET and RDSET

RSET (pin 12) and RDSET (pin 13) use external resistors to ground to set the DC current in the device and to optimize the linearity performance of the amplifier stage. The resistor values in Table 8 can be used as a guide for the RF band of interest. By decreasing the resistor value to ground on the RSET pin will increase the DC current in the amplifier stage. The maximum operating DC current through RSET should never be higher than 1.5mA at T<sub>EP</sub>= 105 °C. The resistor to ground on RDSET is used to optimize the linearity performance in conjunction with the resistor on RSET.